



Vertex & tracking detector For EicC

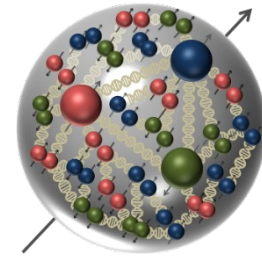
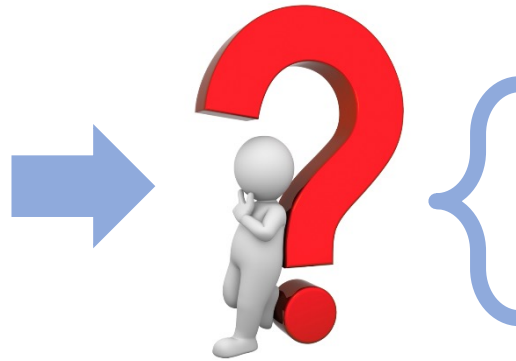
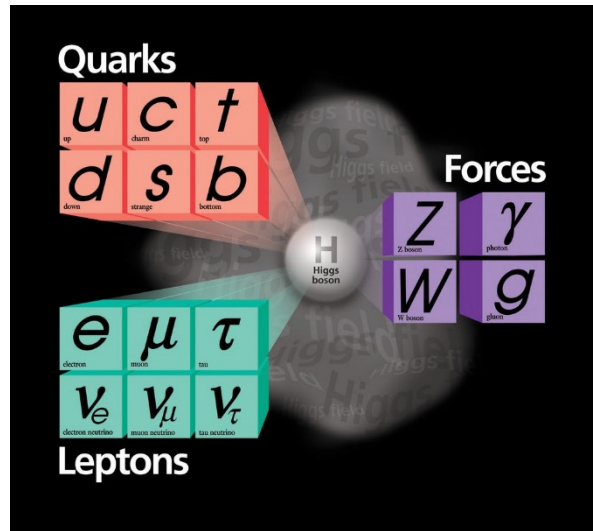
报告人：郭爱强¹ 赵承心¹ 王亚平²

1 中科院近物所-夸克物质中心

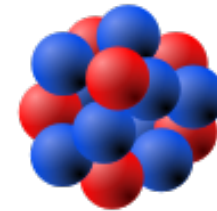
2 华中师范大学-物理科学与技术学院

第三届半导体辐射探测器研讨会-2023-05

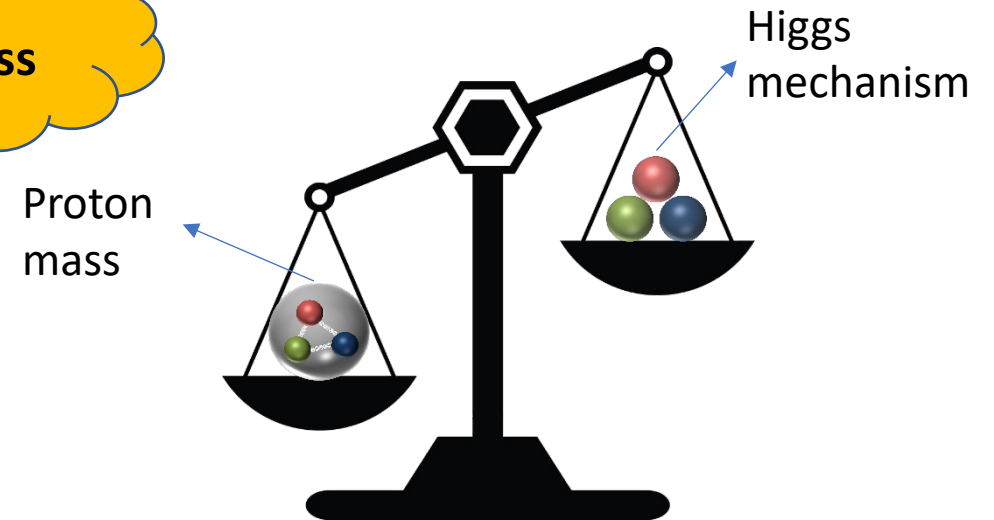
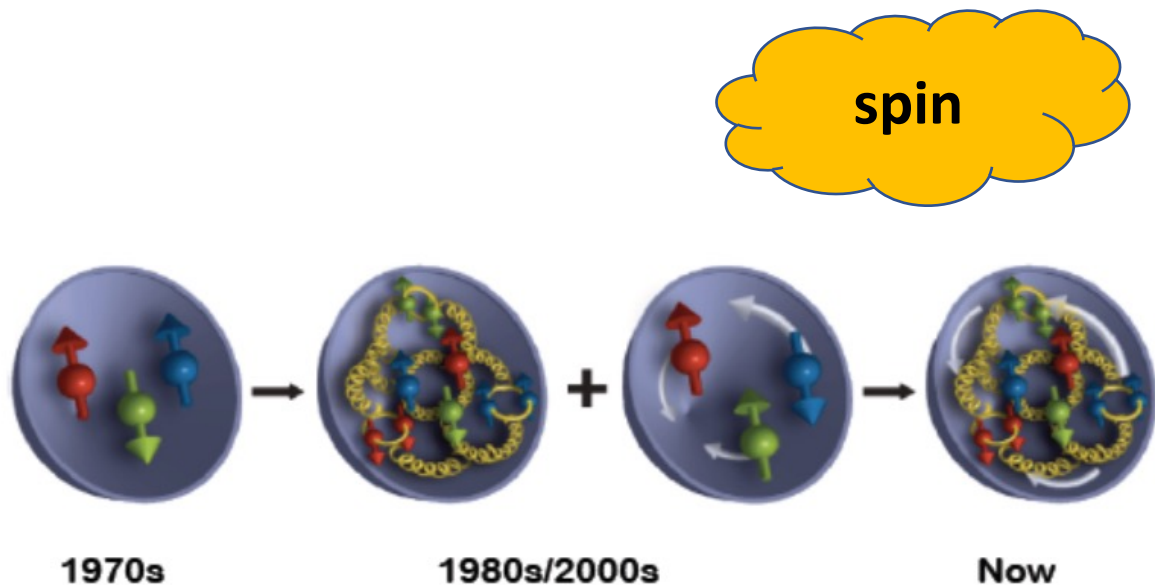
We know very little...



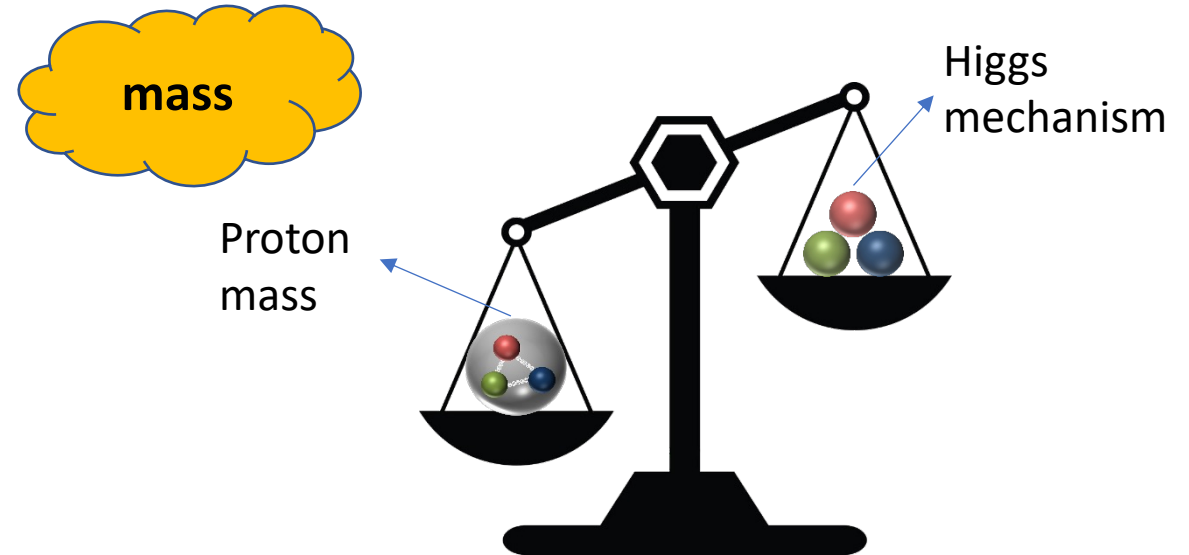
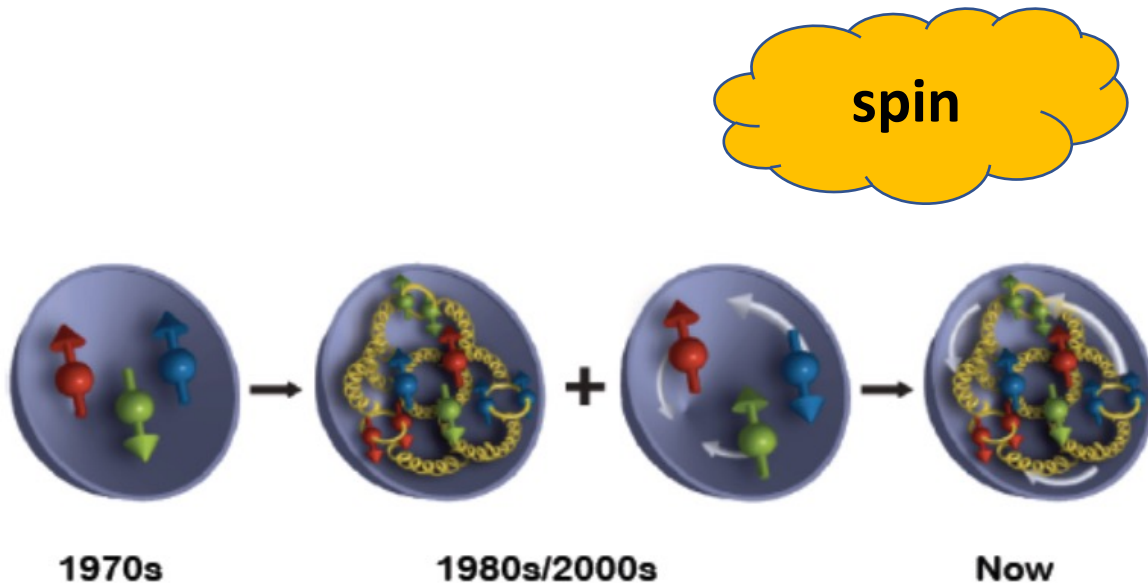
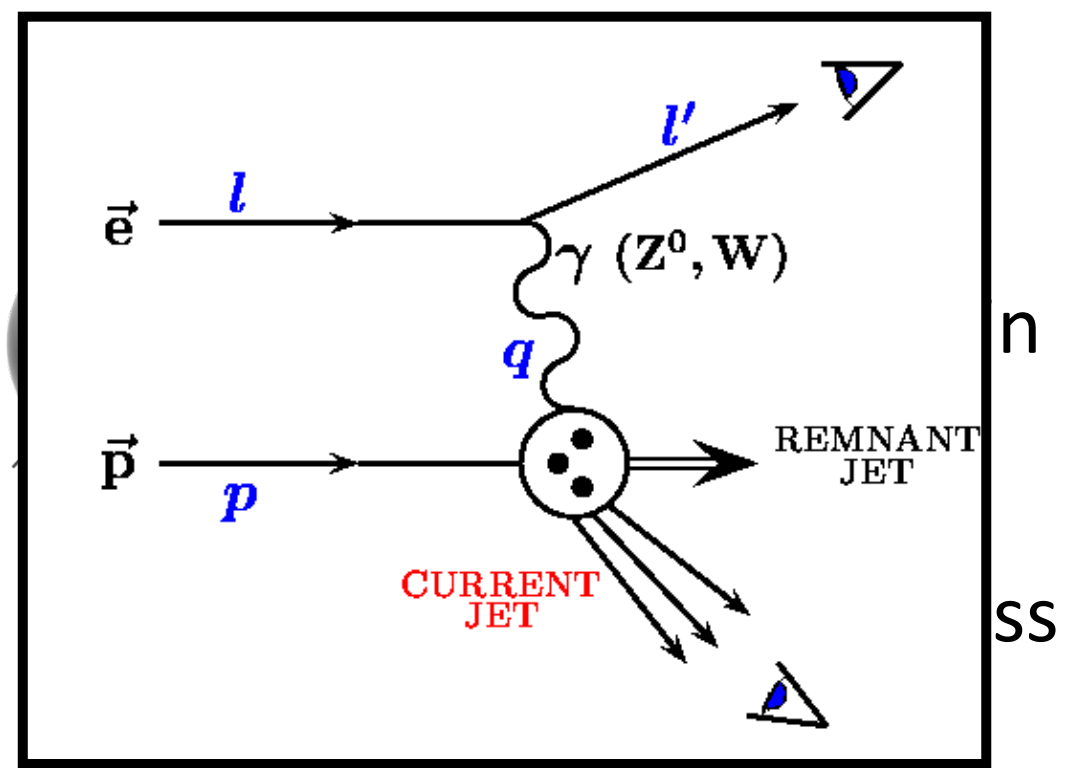
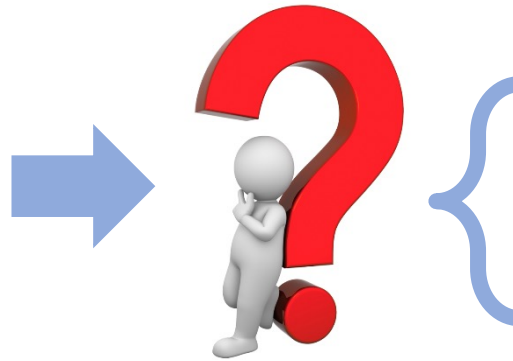
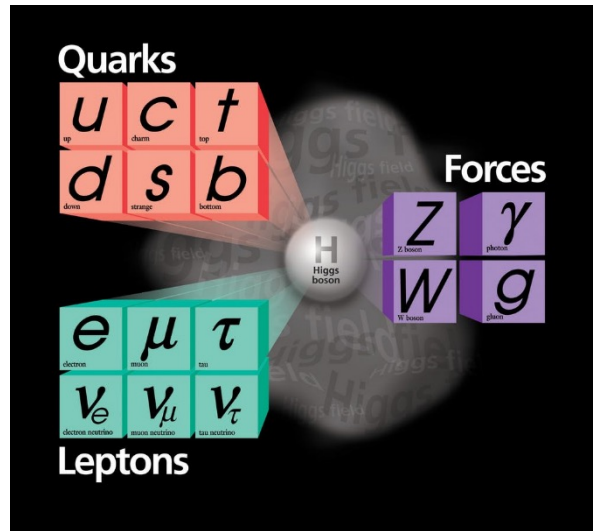
Origin of nucleon spin



Origin of nucleon mass



We know very little...



Electron Ion Collider in China...Huizhou(惠州) in Guangdong province



装置区



总部区

HIAF under construction

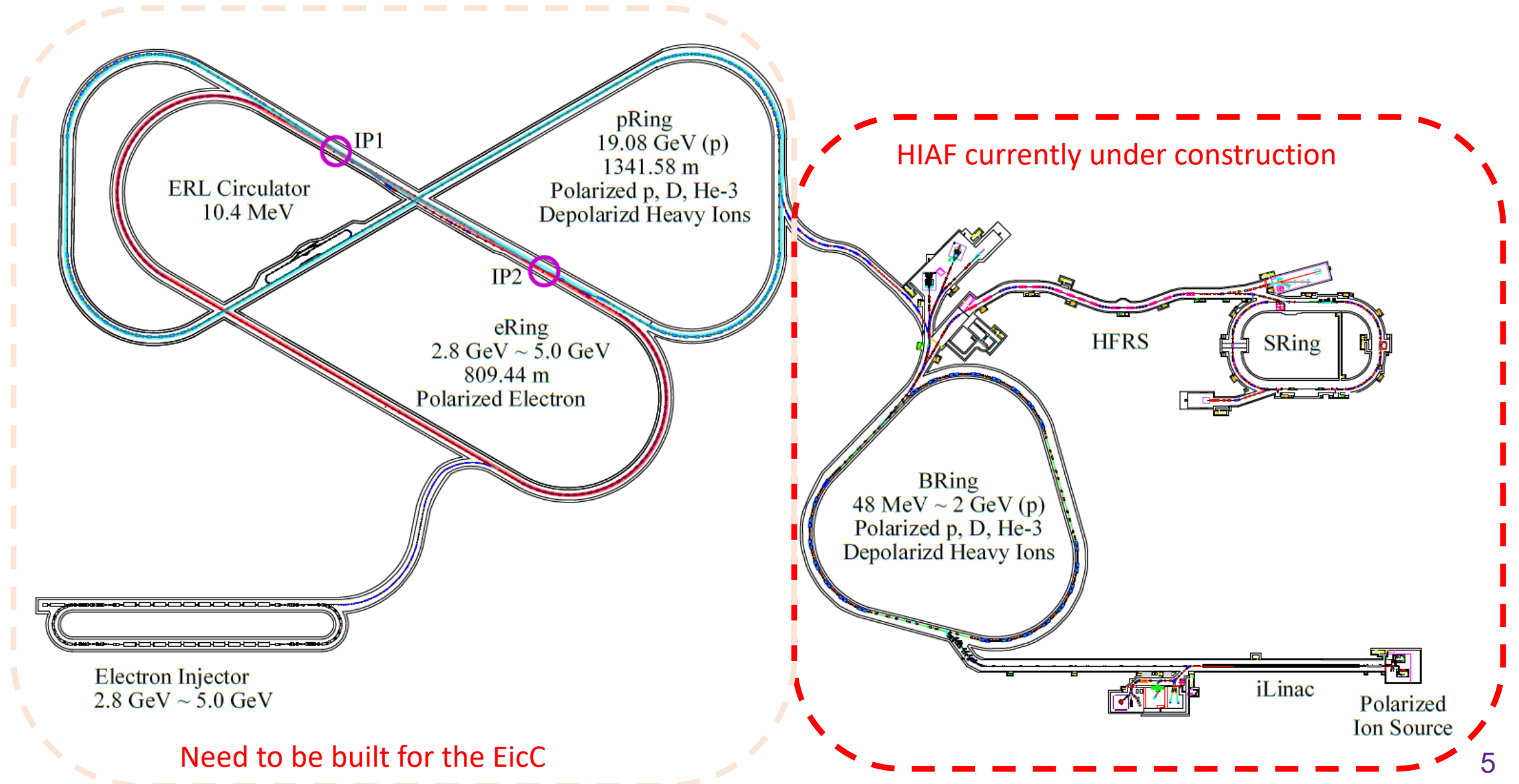


EIC in China

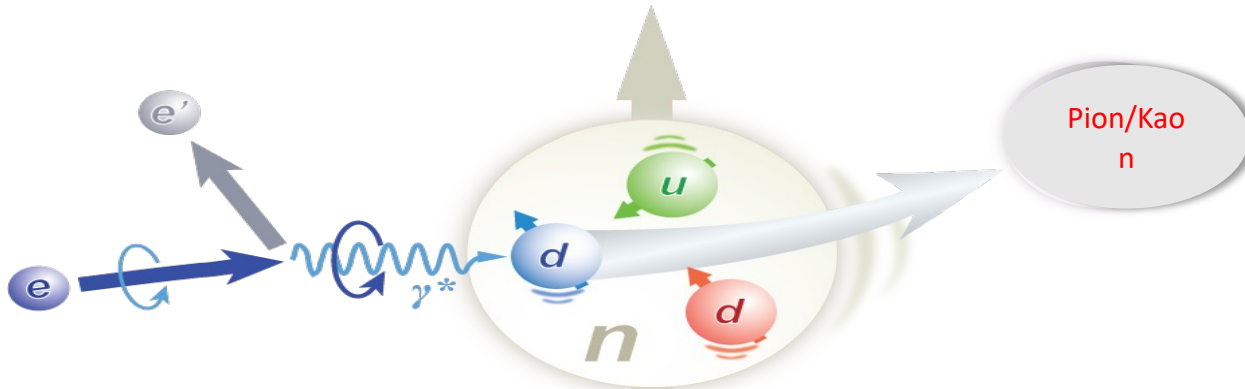
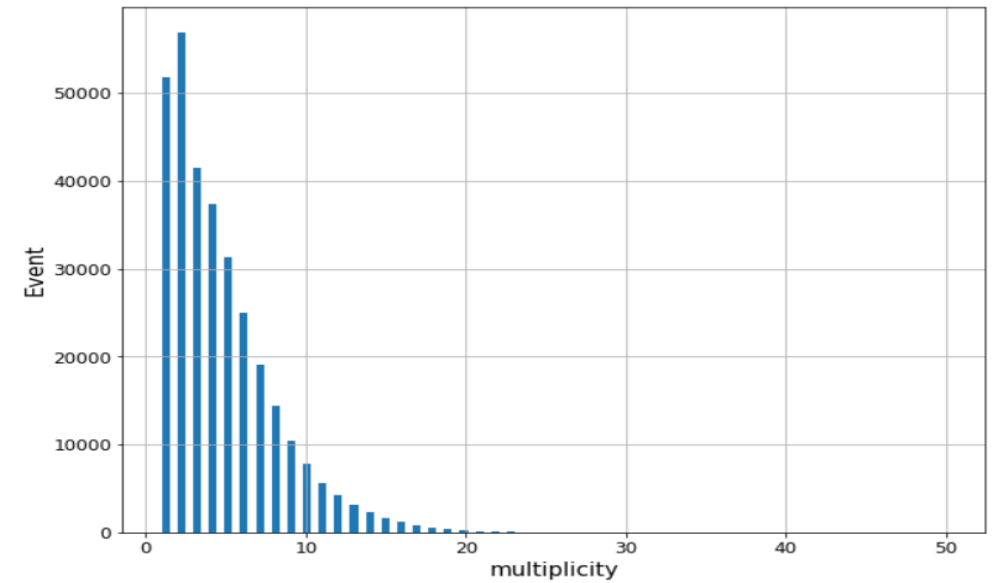
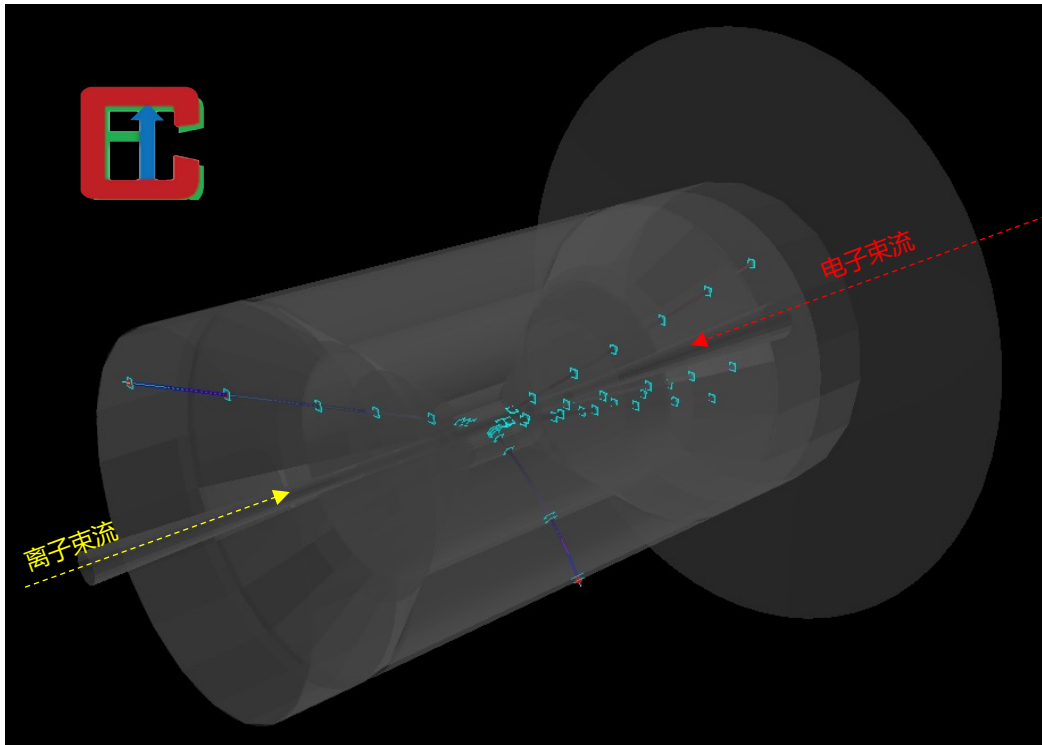


Electron Ion Collider in China, EicC

EicC Accelerator complex layout



Data sample @ EicC



- **3.5x20 GeV** e-p collision with center of mass energy of 16.7 GeV
- A cross-section of 20.8 μb .
- The luminosity is $L = 2 \times 10^{33} \text{ cm}^{-2}\text{s}^{-1}$
- Expect to collect 50 fb^{-1} per year

The requirement on EicC

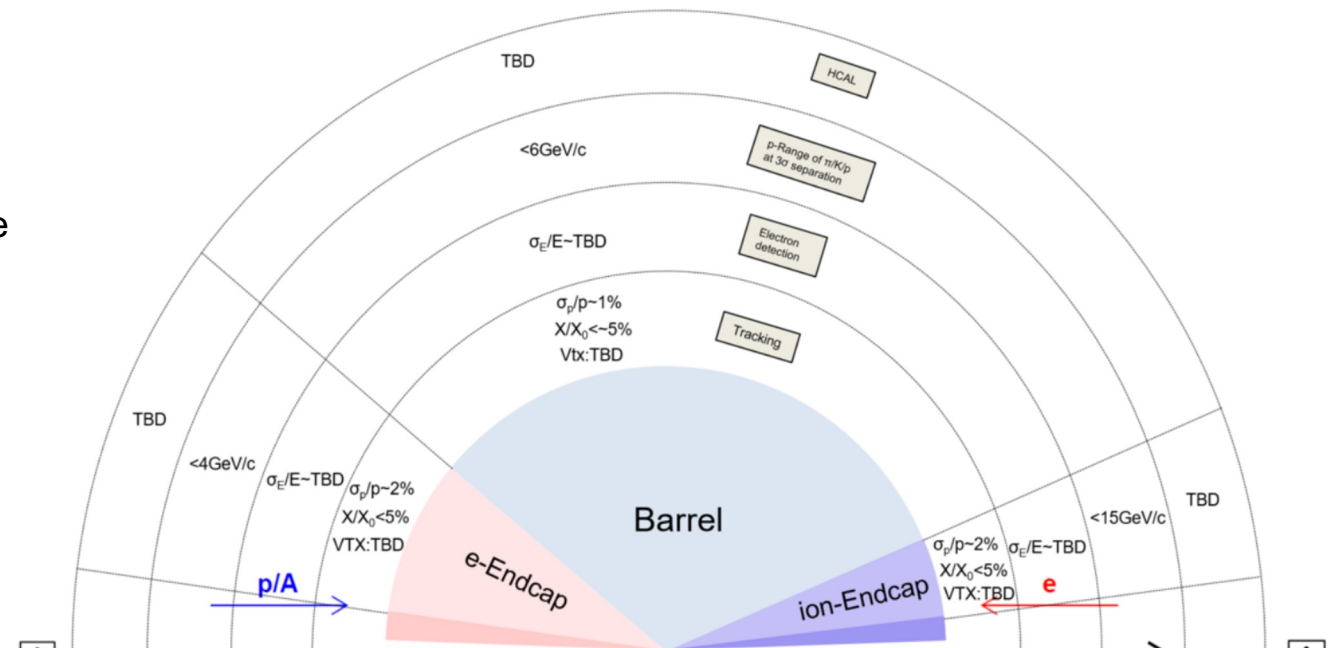
Goal of vertex and tracking system

- Reconstruct charged-particle trajectories
 - Join hits to form a track
 - measure momentum and charge (with magnetic field)
- Reconstruct vertices
 - “primary” vertex: collision point where most particle are produced
 - “secondary” vertices: decay of unstable particles

Physics requirements for EicC →

- Barrel ($-1 < \eta < 1.6$):
 - $\frac{\sigma_p}{p} < 1\% @ 1GeV$; $\frac{X}{X_0} < 5\%$;
- e-endcap ($-3 < \eta < -1$):
 - $\frac{\sigma_p}{p} < 2\% @ 1GeV$; $\frac{X}{X_0} < 5\%$;
- Ion-endcap ($1.6 < \eta < 3$):
 - $\frac{\sigma_p}{p} < 2\% @ 1GeV$; $\frac{X}{X_0} < 5\%$;
- Assume $B \sim 1.5$ T

Front. Phys. 16(6), 64701 (2021)

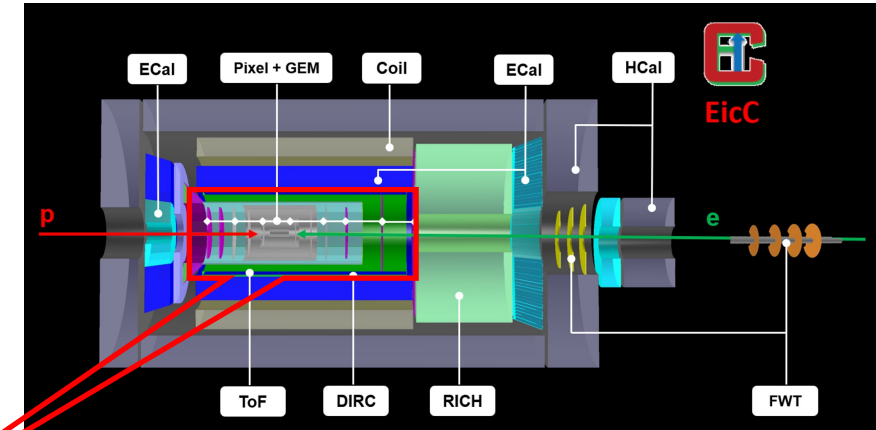
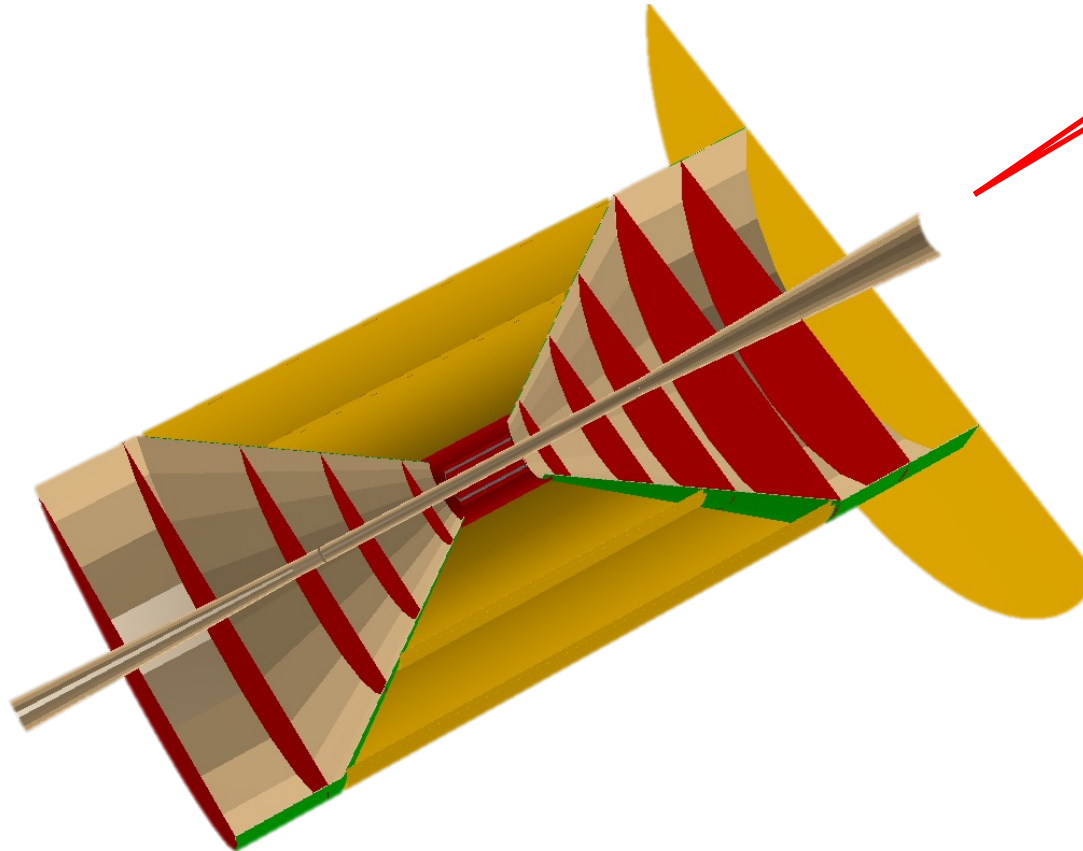


- The event rate of 83.2 kHz.
- the final state particles are concentrated near pseudo-rapidity $\eta = 1$, with a particle density rate of $dN/d\eta dt = 8 \times 10^4/s$.

The vertex and tracking detector @ EicC

EicC vertex&tracking system:

- The core detector of EicC
- Measure the vertex and momentum of charged tracks

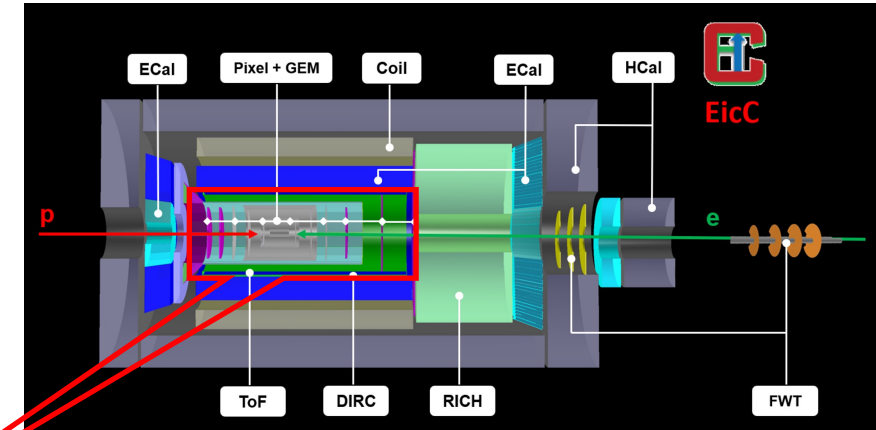
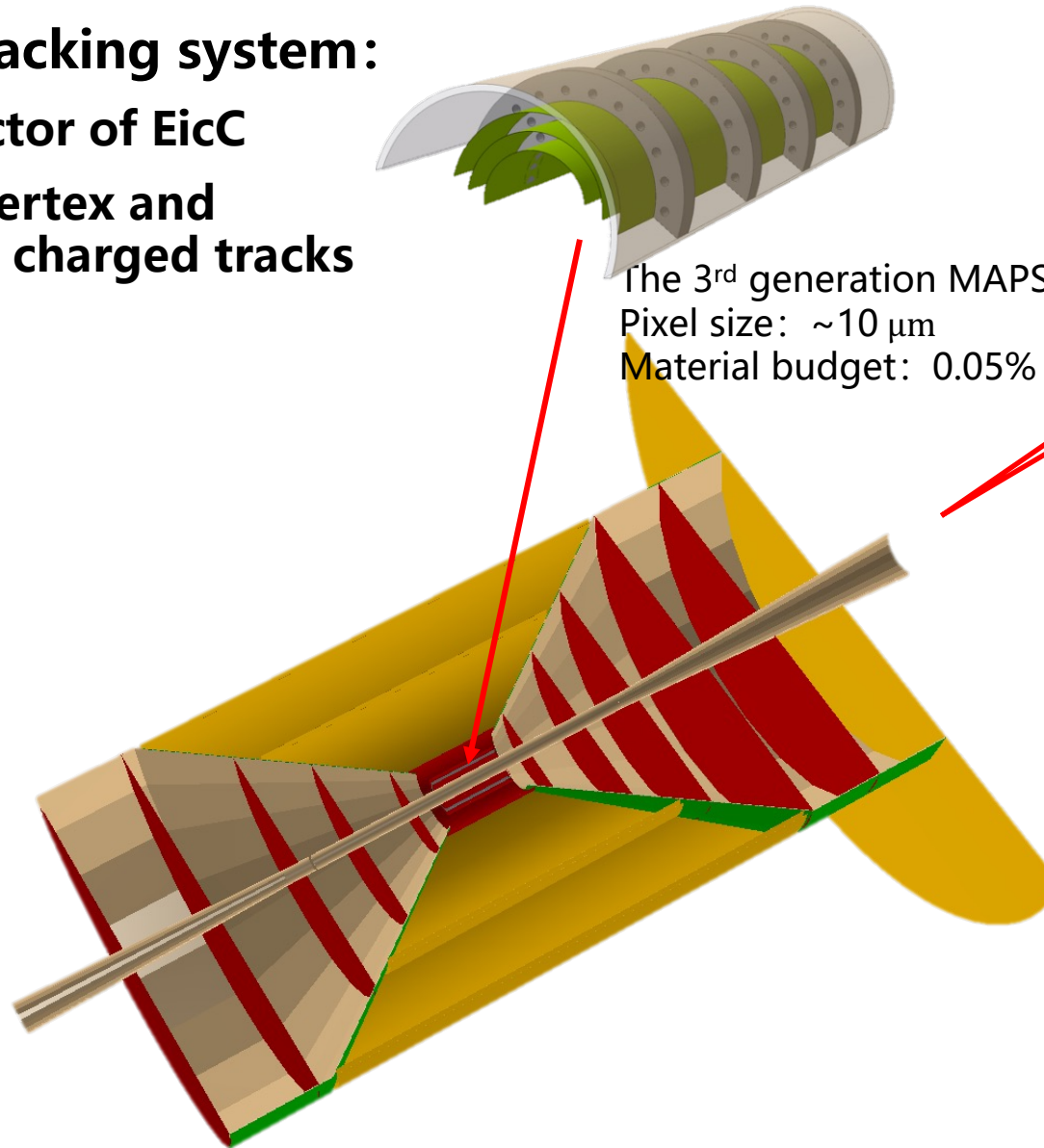


EicC conceptual design

The vertex and tracking detector @ EicC

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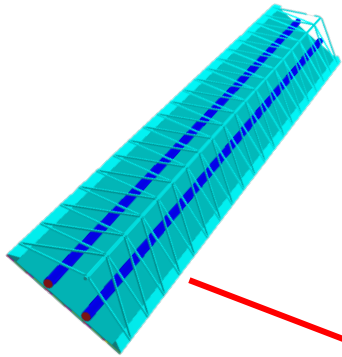


EicC conceptual design

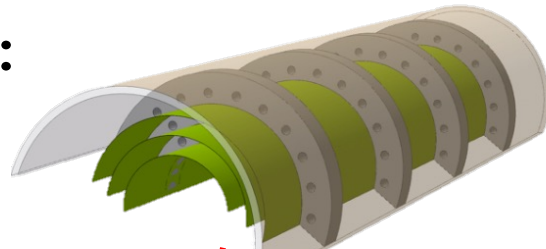
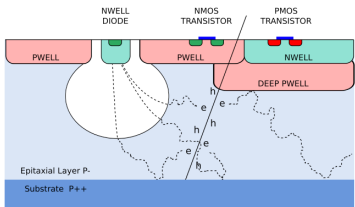
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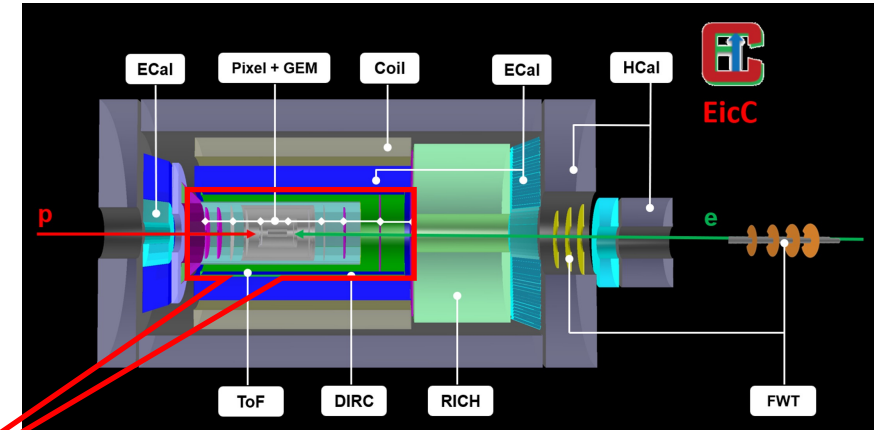
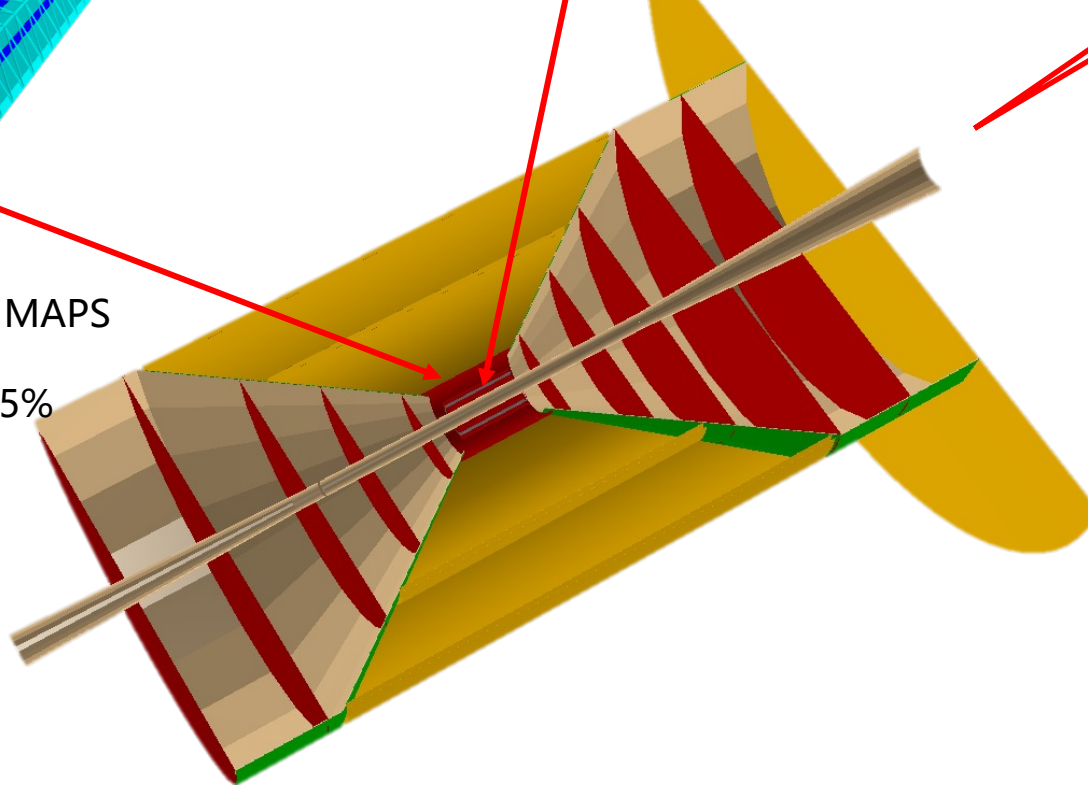
- The core detector of EicC
- Measure the vertex and momentum of charged tracks



The 1st generation of MAPS
Pixel size: $\sim 30\ \mu\text{m}$
Material budget: 0.55%



The 3rd generation MAPS
Pixel size: $\sim 10\ \mu\text{m}$
Material budget: 0.05%

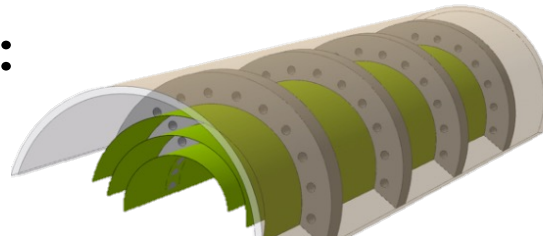


EicC conceptual design

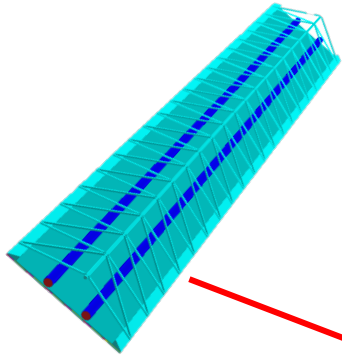
The vertex and tracking detector @ EicC

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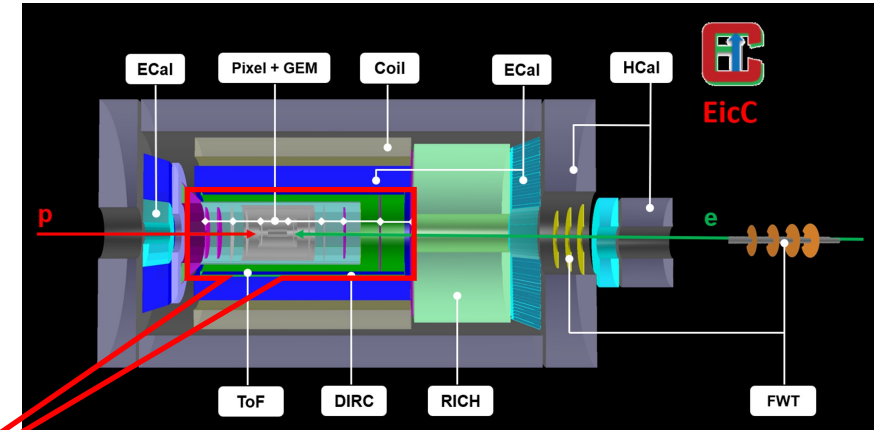
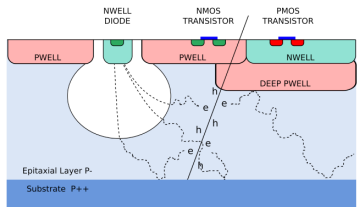
- The core detector of EicC
- Measure the vertex and momentum of charged tracks



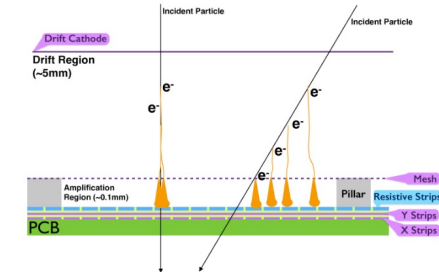
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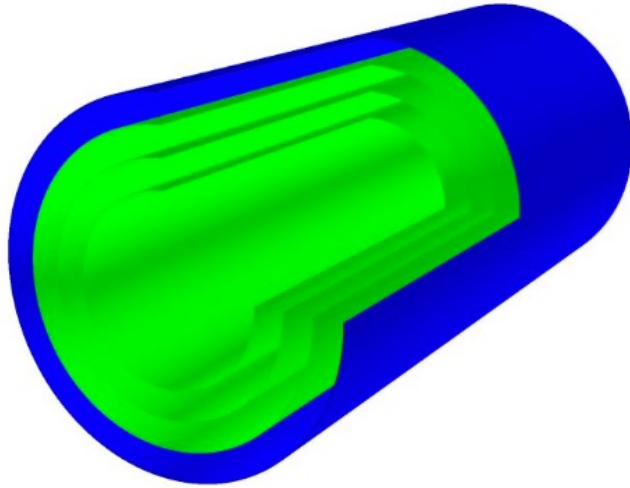
EicC conceptual design



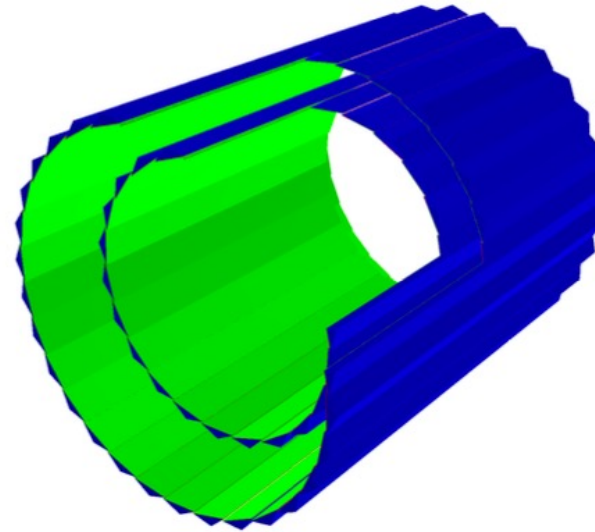
MPGD detector
Spatial resolution : $\sim 150\ \mu\text{m}$
Material budget : 1%

The silicon components

3 ITS3 Layers + Support Layer



2 ITS2 Layers with Support Structure



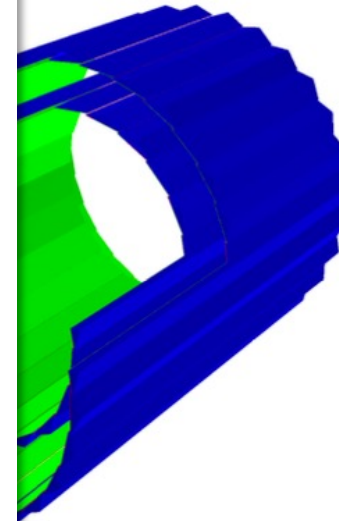
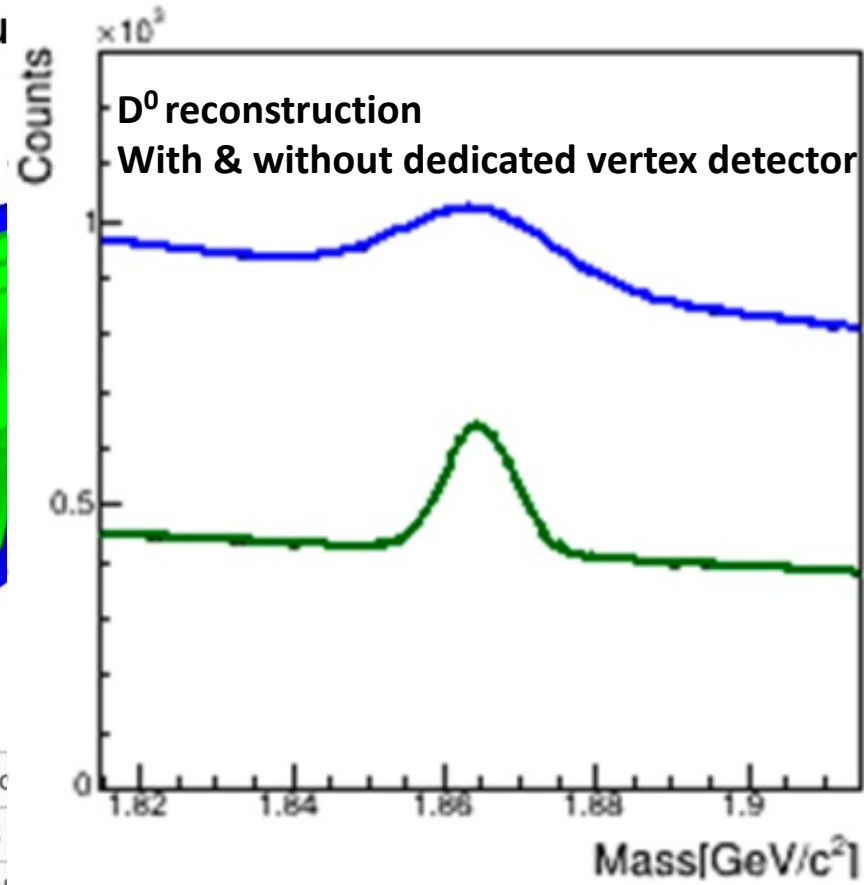
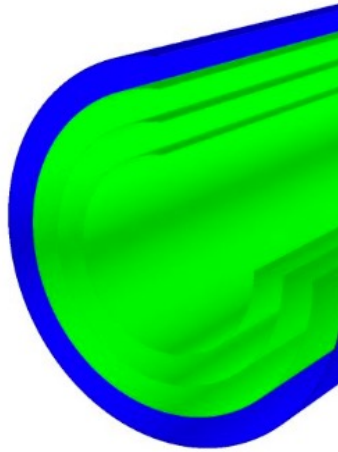
Silicon Tracker (3 Vertex + 2 Barrel Layers)

R (cm)	Length (cm)	Resolution	Active Area Material (X/X0 %)
3.3	28.0	10 um pixel pitch	0.05
4.35	28.0	10 um pixel pitch	0.05
5.4	28.0	10 um pixel pitch	0.05
13.34	34.34	10 um pixel pitch	0.55
17.96	46.68	10 um pixel pitch	0.55

The silicon components

3 ITS3 Layers + Su

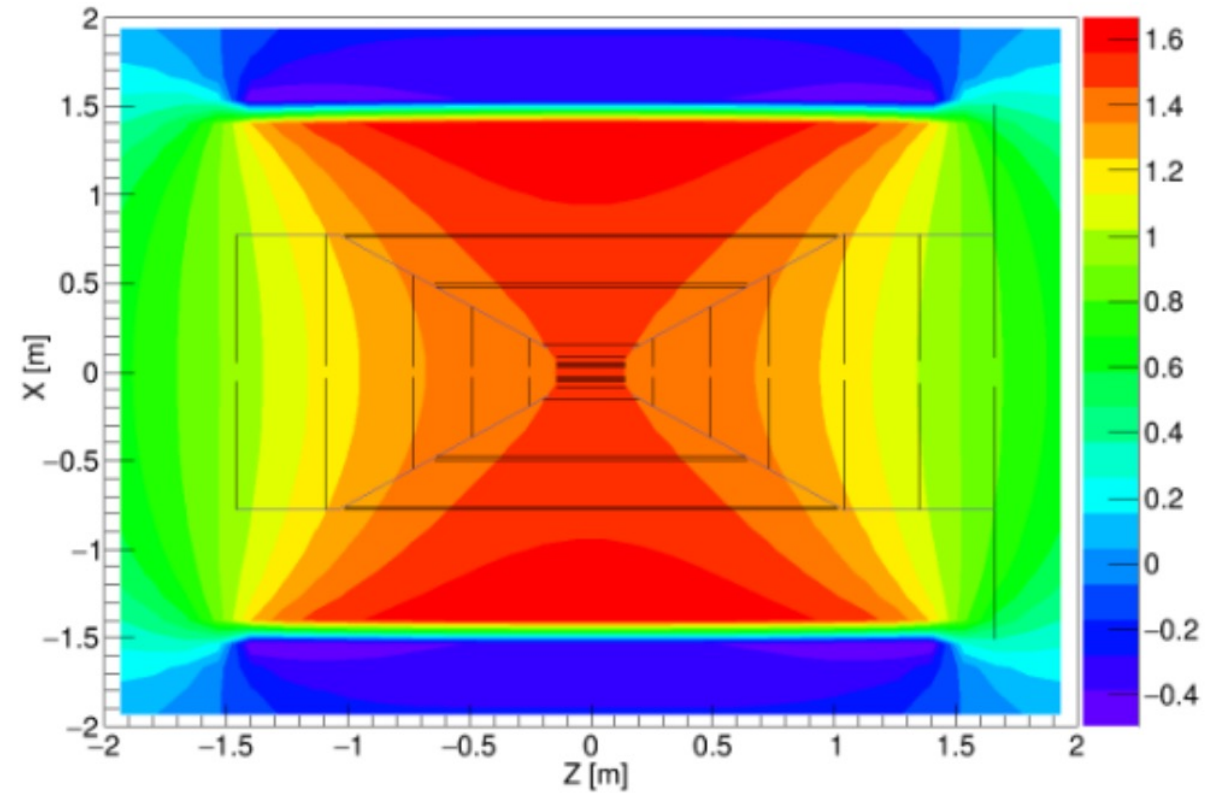
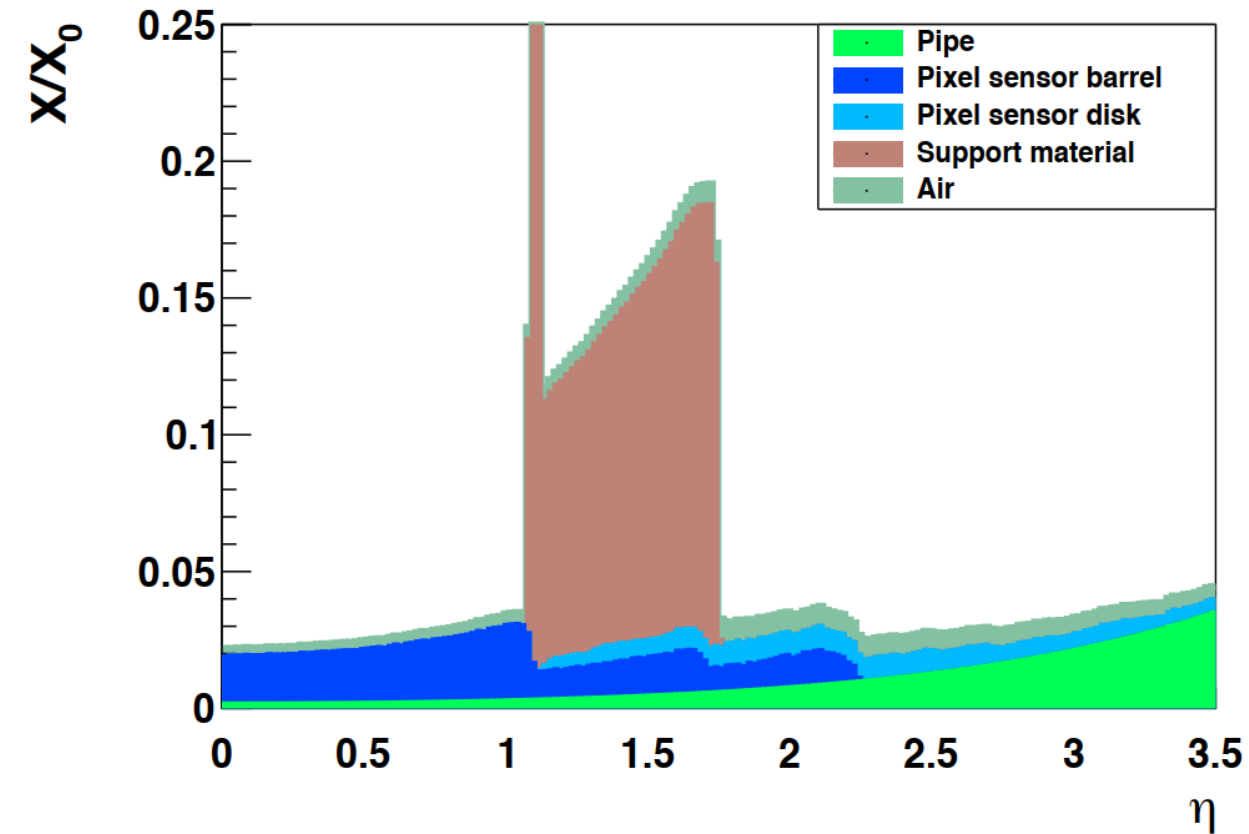
h Support Structure



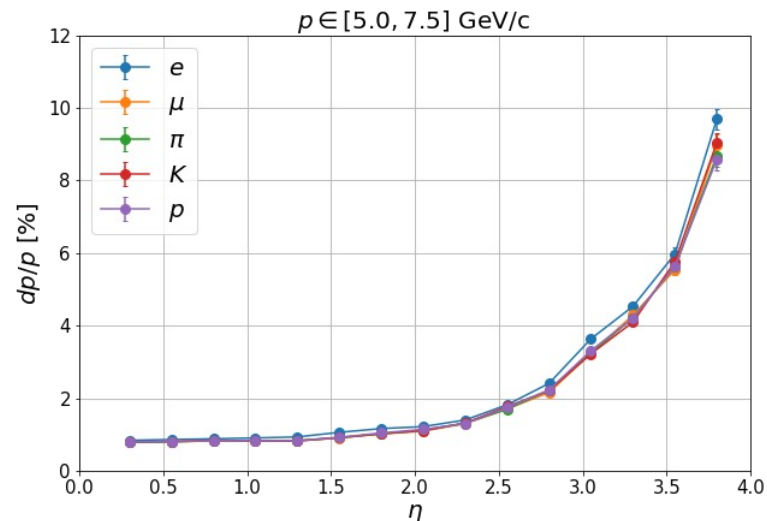
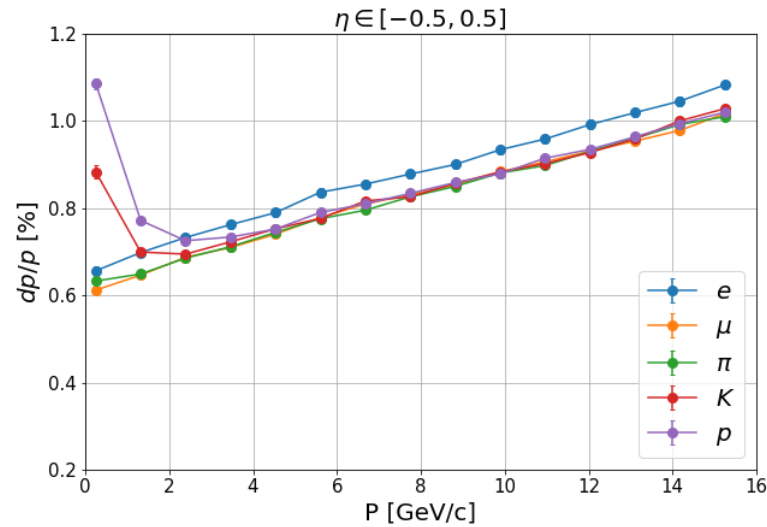
R (c			
3.3			
4.3!			
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Material budget vs η and B field

(a) Radiation length vs η



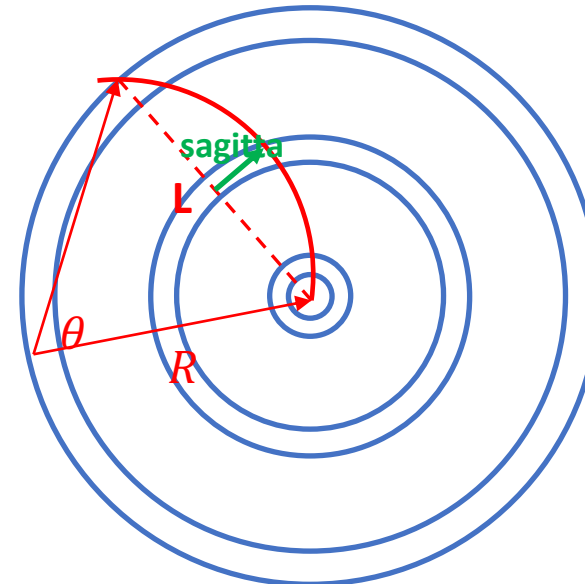
The momentum resolution



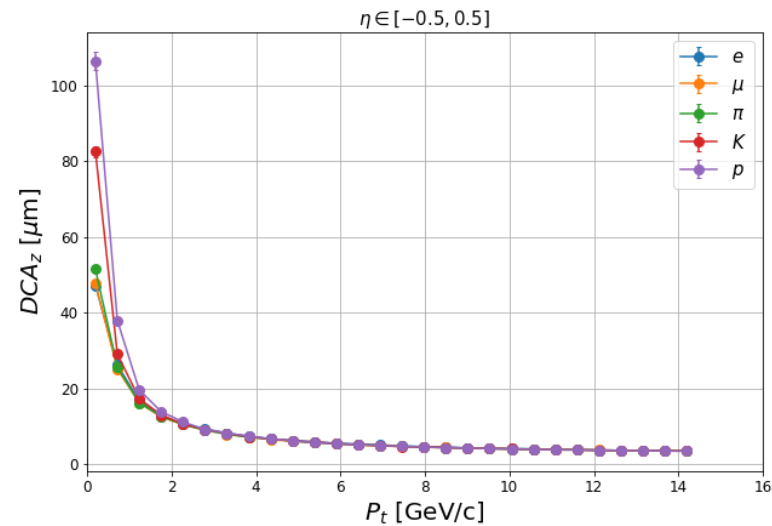
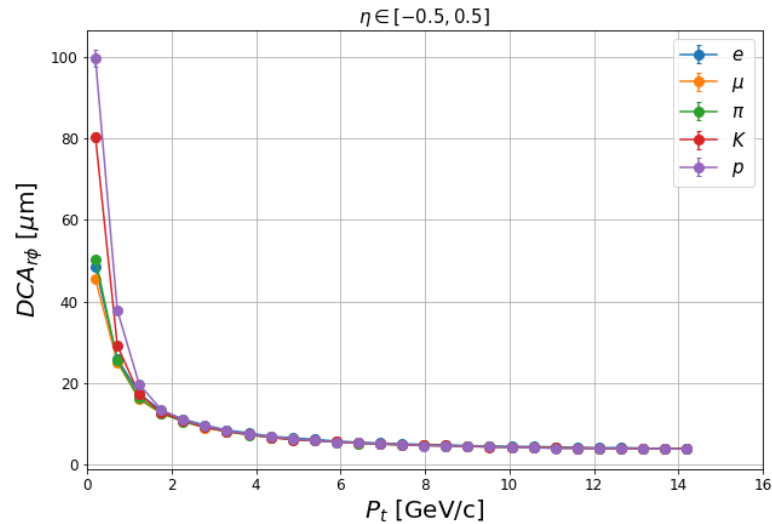
The momentum of a charged track is determined by its trajectory (curvature)

- The formula: $p = 0.3 RB$, R is the radius of the track, B is the intensity of the magnetic field
- Practically, we measure the sagitta to determine the R :
- The relative momentum resolution is:

$$\frac{\sigma_p}{p} = \frac{\sigma_s}{s} = \frac{8p}{0.3BL^2} \sigma_s$$



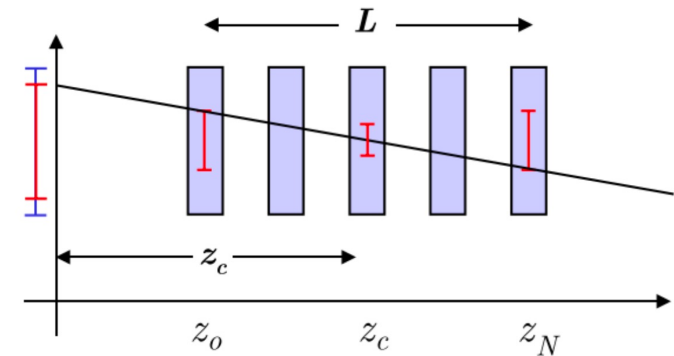
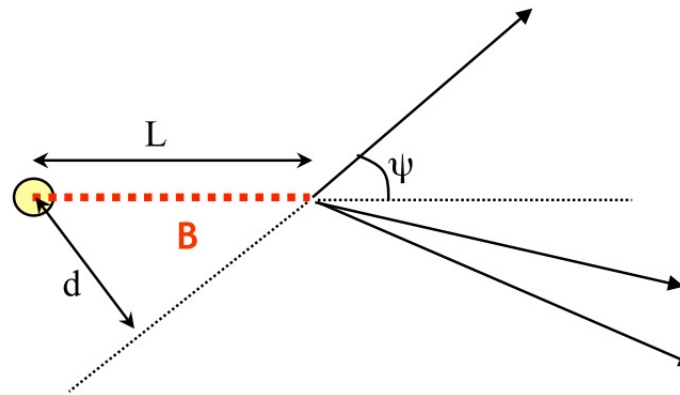
The vertex resolution



The impact parameter d :

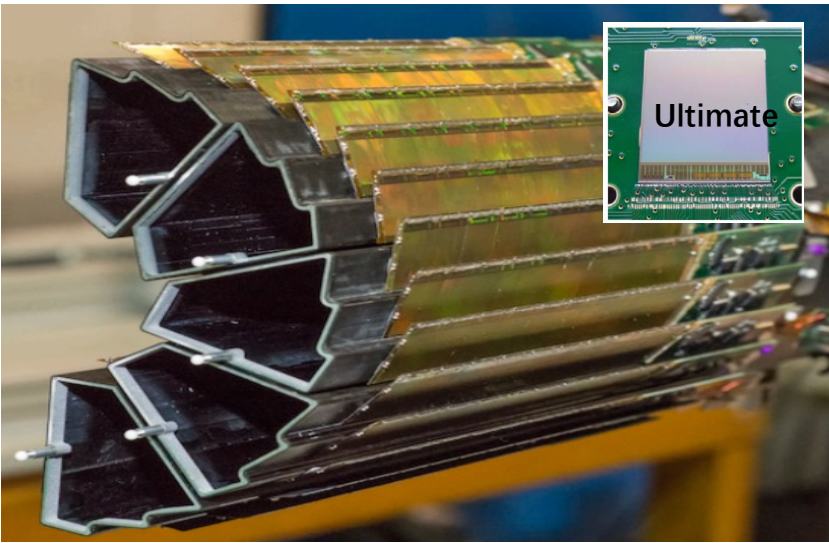
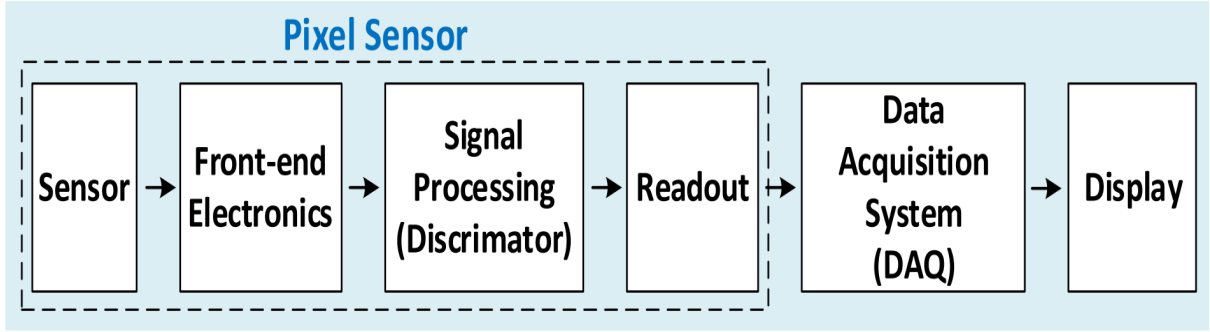
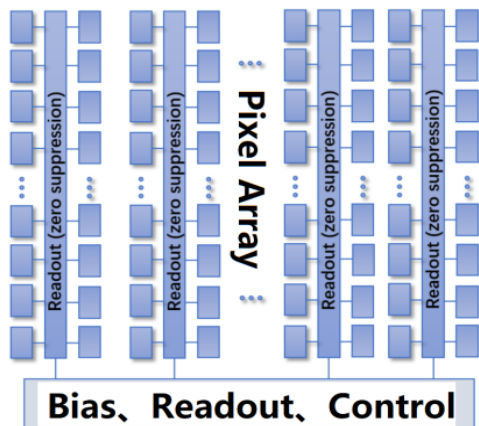
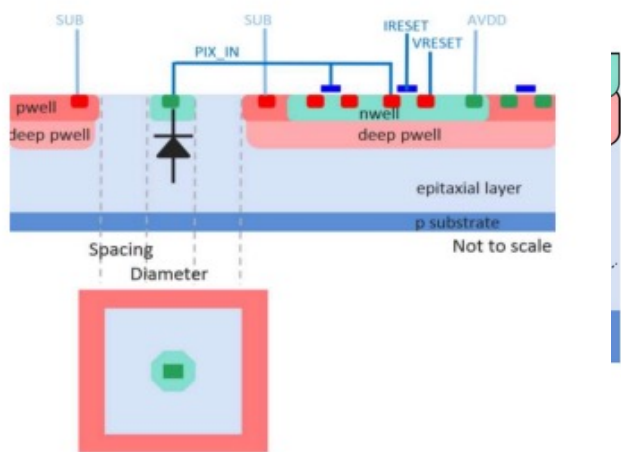
- $d = L \sin \psi$
- ψ is due to multiple-scattering and detector resolution
- In the case of equal spacing detector and equal errors σ
- The uncertainty of measurement on vertex (details in backup):

$$\sigma_{vertex}^2 = \frac{\sigma^2}{N+1} + \frac{\sigma^2}{N+1} \frac{12N}{N+2} \frac{Z_c^2}{L^2}$$

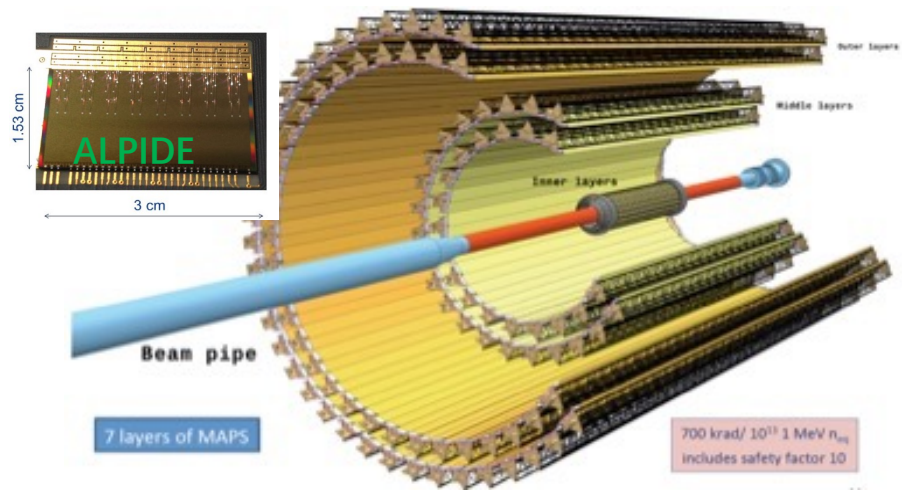


The Monolithic Active Pixel Sensor

CMOS Pixel Sensors \equiv Detector \oplus Front-End Electronics in same die



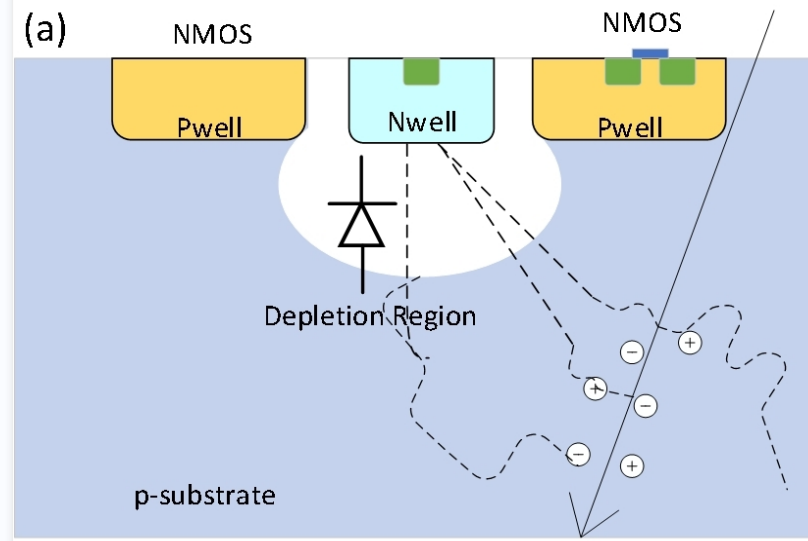
STAR HFT (世界上首个像素探测器)
400片MAPS, 360M pixels



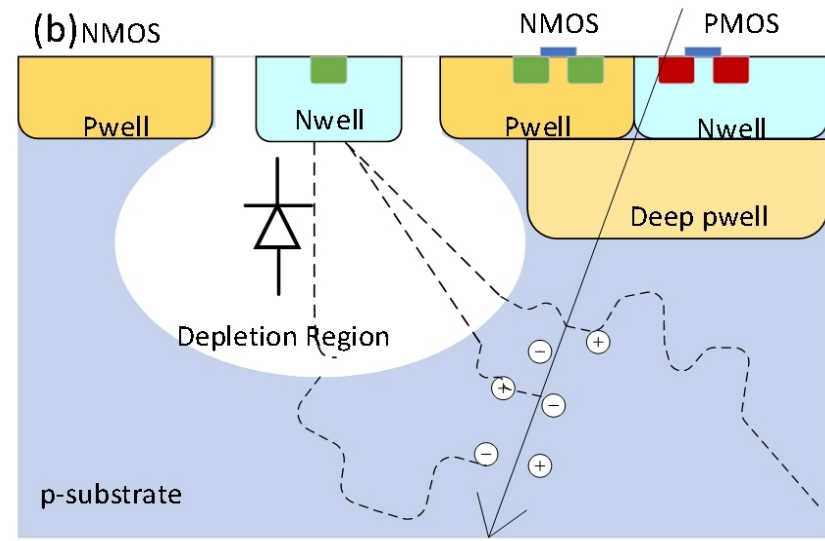
ALICE ITS 探测器 (目前最大规模像素探测器)
24142块MAPS, ~10m², 12.5G pixels

TCAD simulation

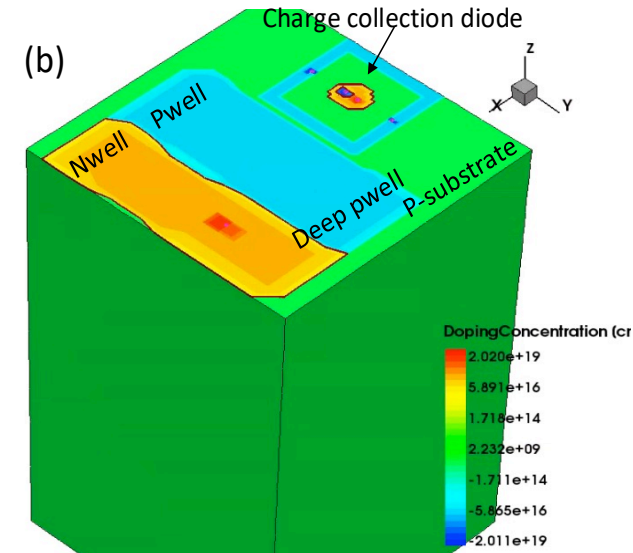
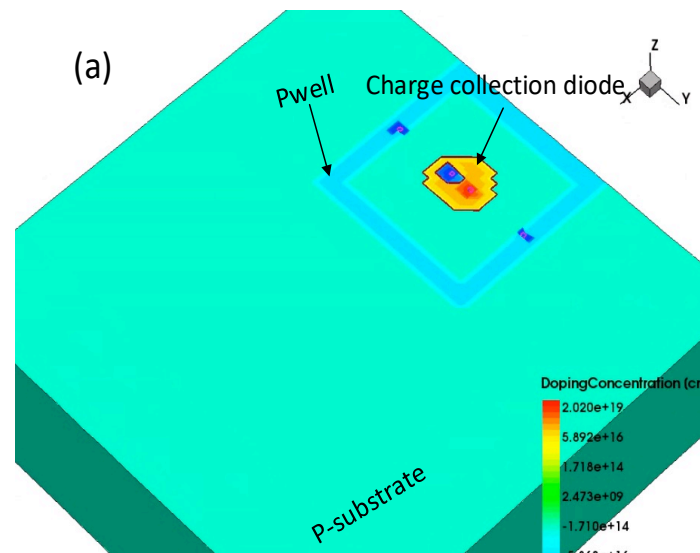
HFT tech.



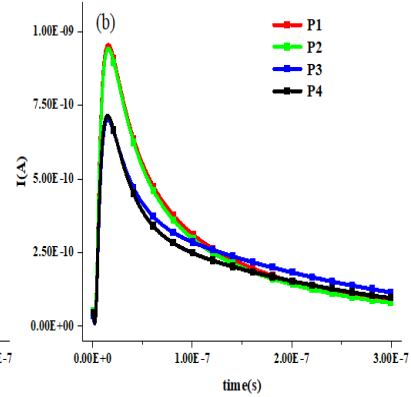
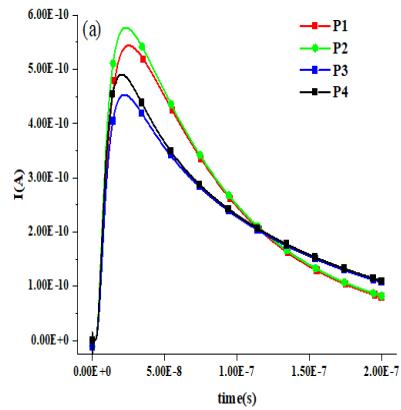
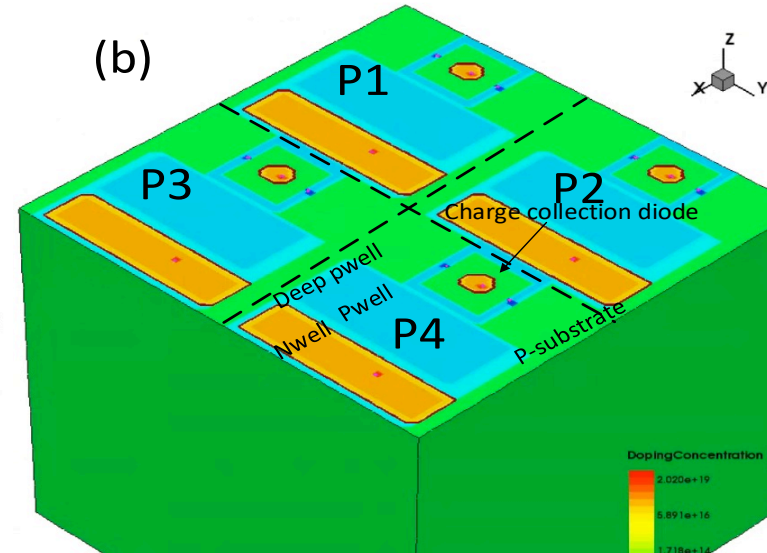
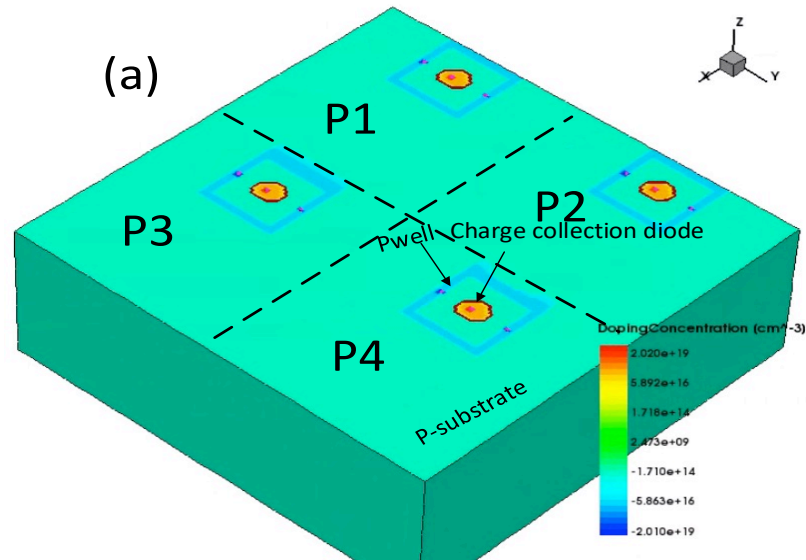
ITS tech.



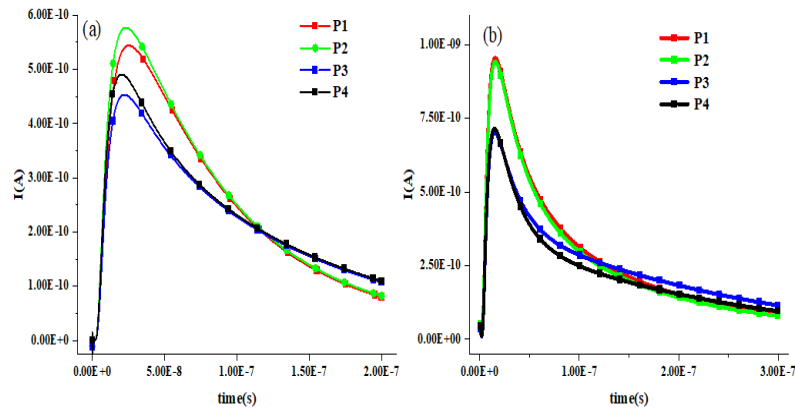
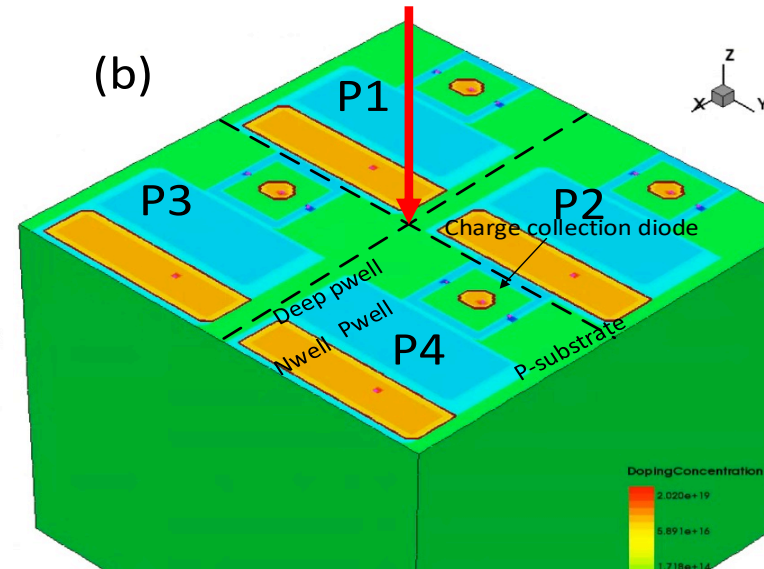
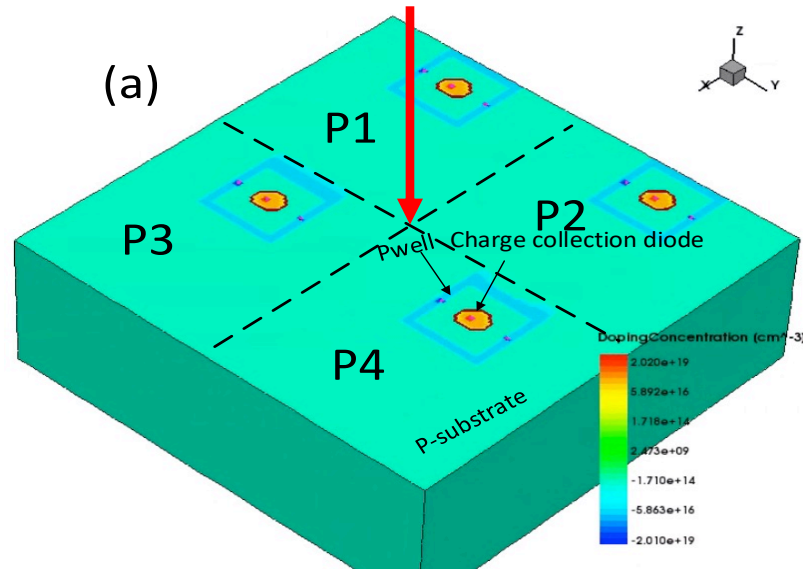
工艺选择和比较：标准双阱工艺 vs 四阱工艺



TCAD simulation



TCAD simulation

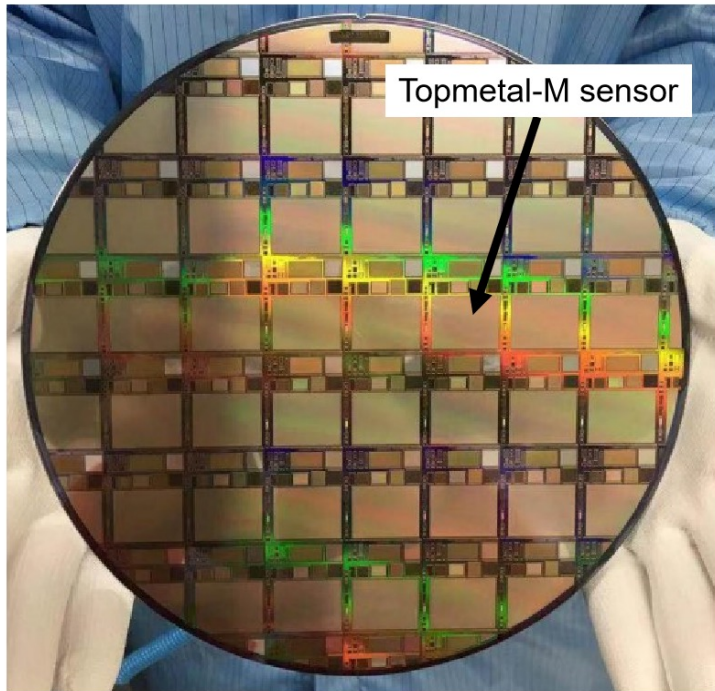


Pixel ID		P1	P2	P3	P4
Charge collection	Twin-wellLR process	329	340	300	308
	Quad-wellHR process	551	530	499	450

50~60% improvement

The first MAPS based on domestic technology

- Topmetal-M

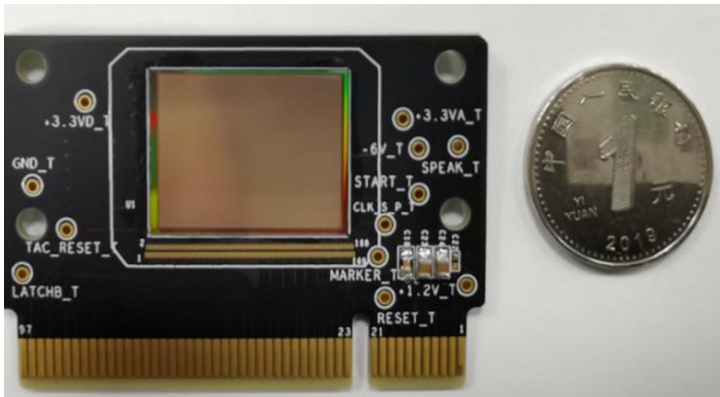


中科院战略先导B” 核物质相结构与重元素合成研究” 专项支持

- 近物所IMP SLIMP & 华师CCNU PLAC
- 基于国内四阱高阻衬底工艺
- 2018.05 - 2019.12设计制造
- 2020.01 - 2021.12测试验证

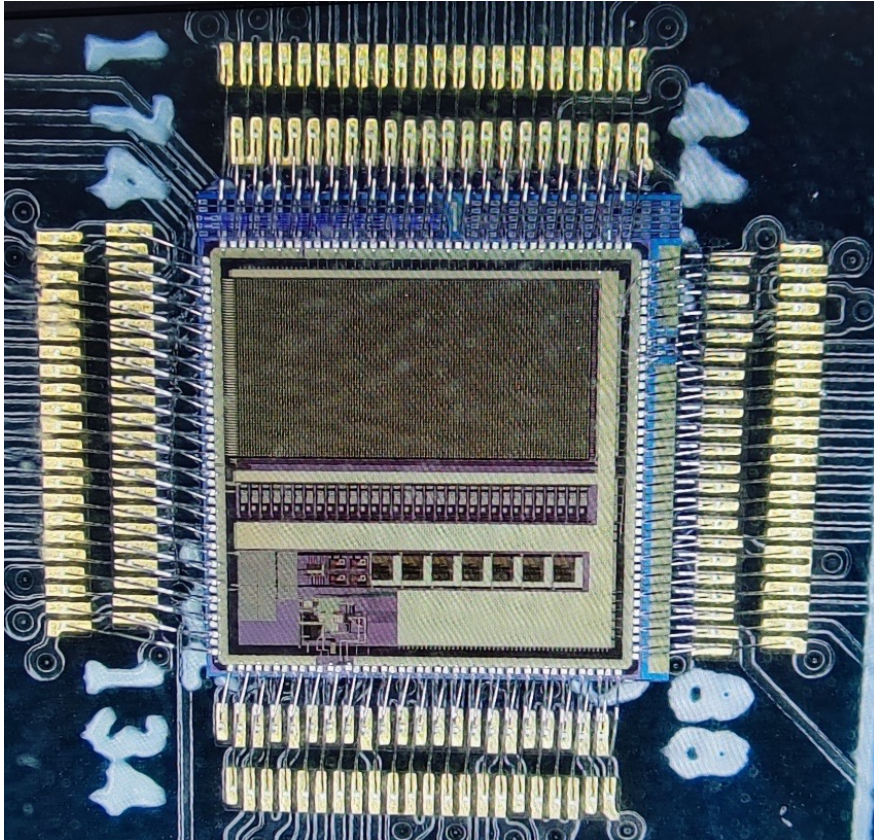
Parameters:

- 像素阵列 512 x 400 Pixels
- 40umx 40um
- Time, Energy and Position Measurement
- Thinned to 100um from backside
- 兼具电荷搜集型Topmetal和MAPS



The full functional MAPS based on domestic technology

- Nupix-A1



□中科院战略先导B” 核物质相结构与重元素合成研究” 专项支持、EicC原型芯片

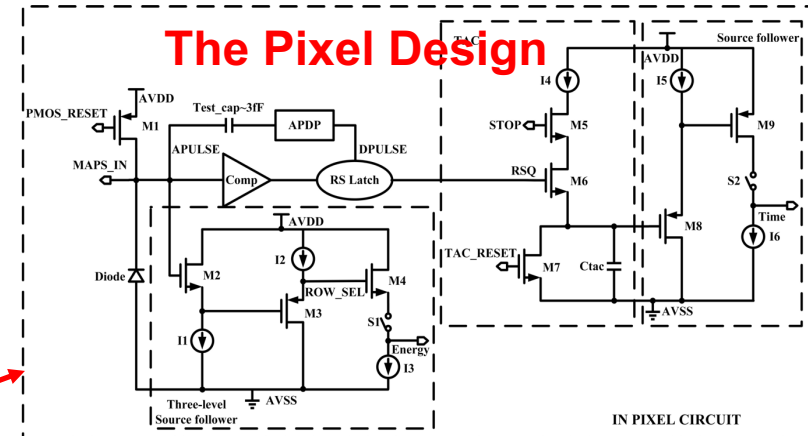
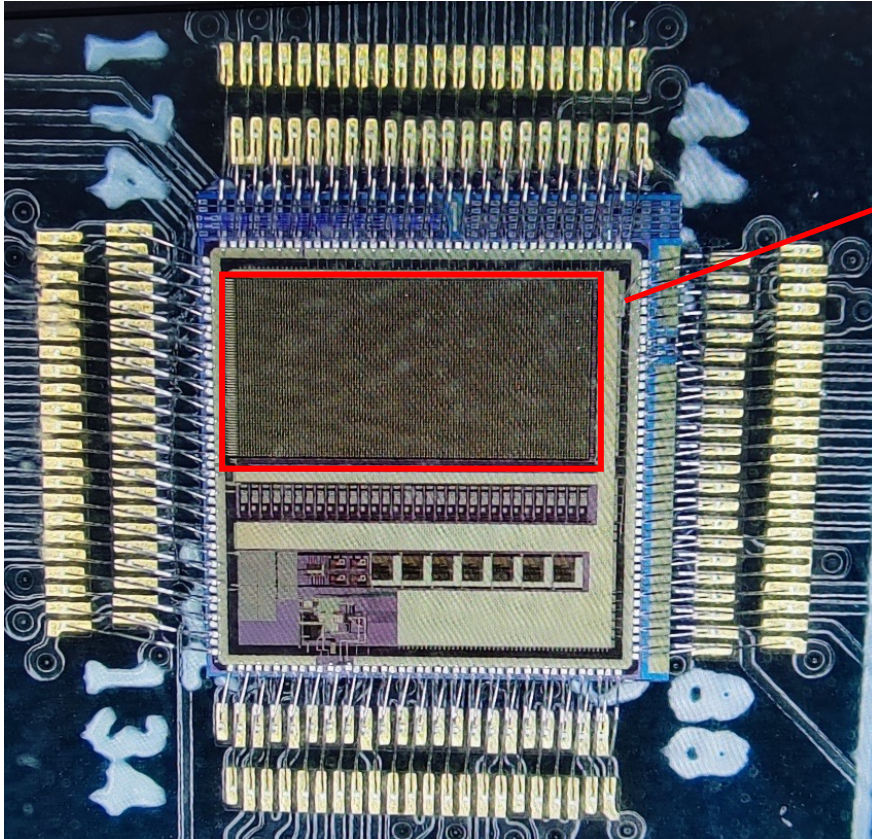
□近物所像素研究室SLIMP牵头研发

□位置、时间和能量测量

□目的：验证基于国内工艺开发复杂度高的像素芯片

The full functional MAPS based on domestic technology

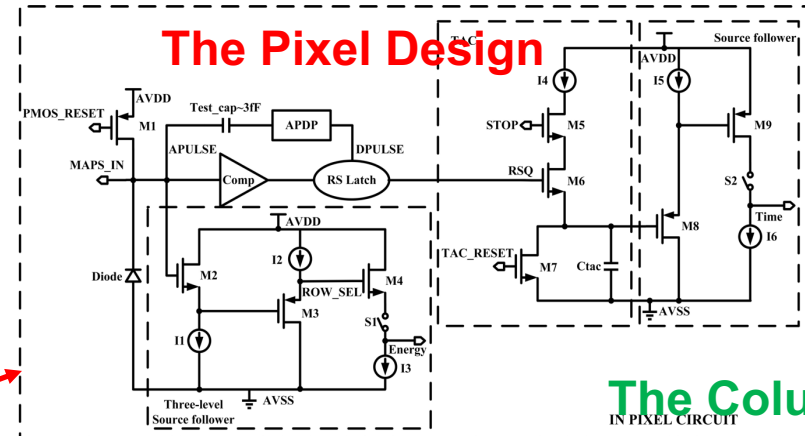
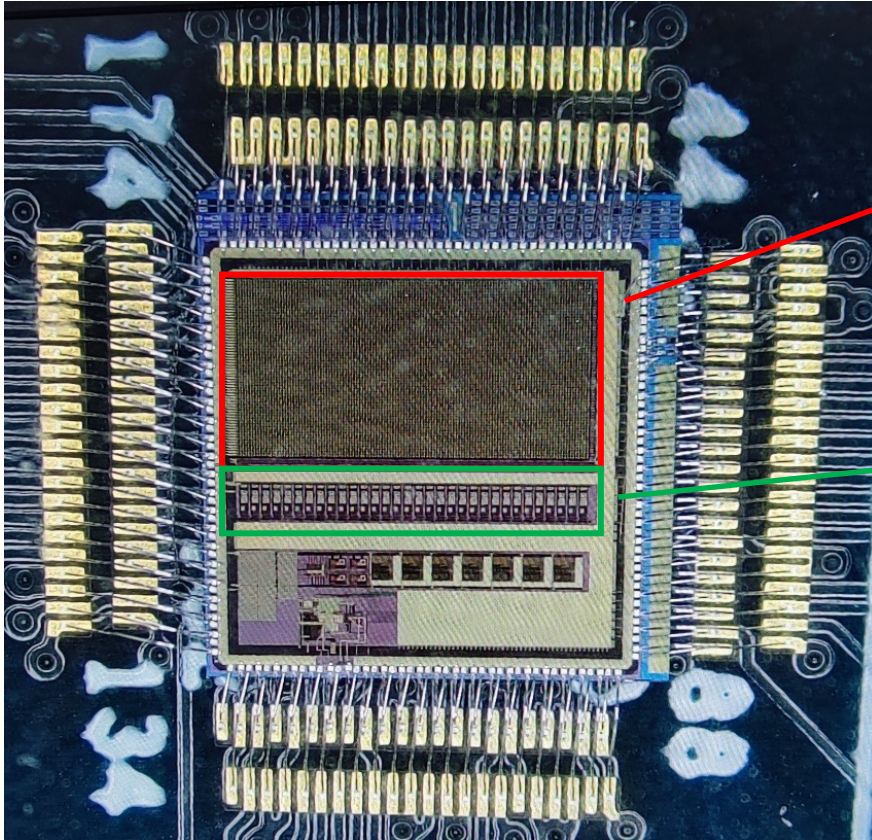
- Nupix-A1



- Pixel Size $30\mu\text{m} \times 30\mu\text{m}$
- Diode area is $10\mu\text{m} \times 10\mu\text{m}$
- Octagon n-well is $3\mu\text{m} \times 3\mu\text{m}$

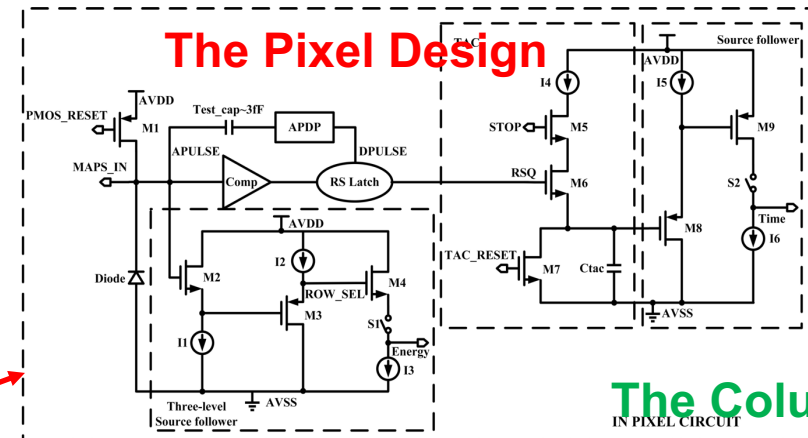
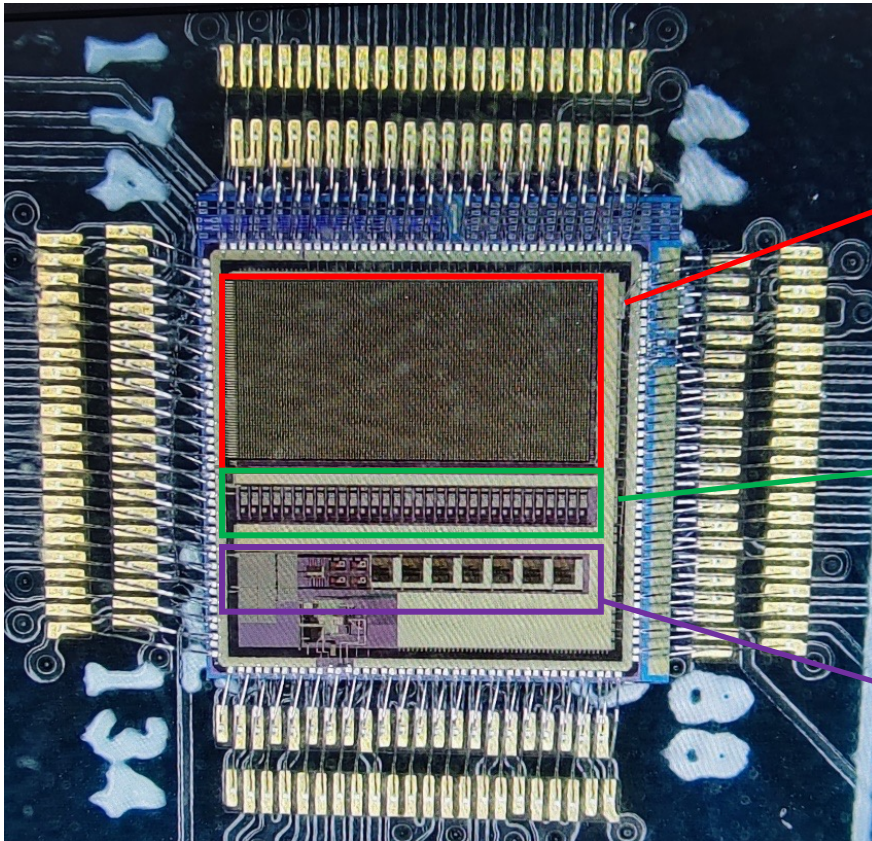
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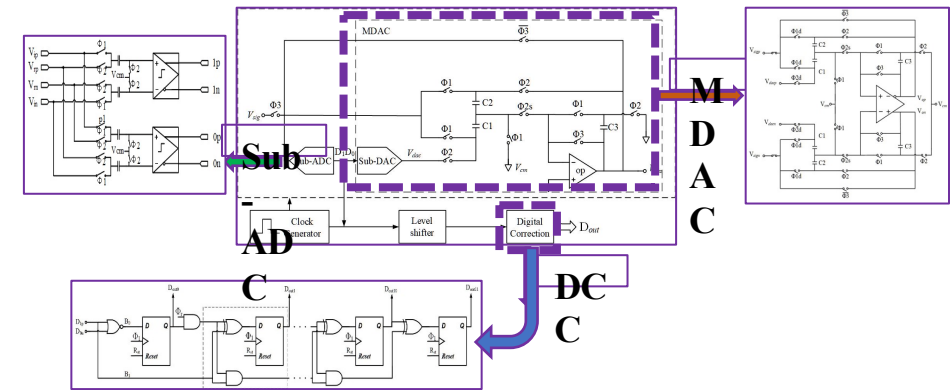
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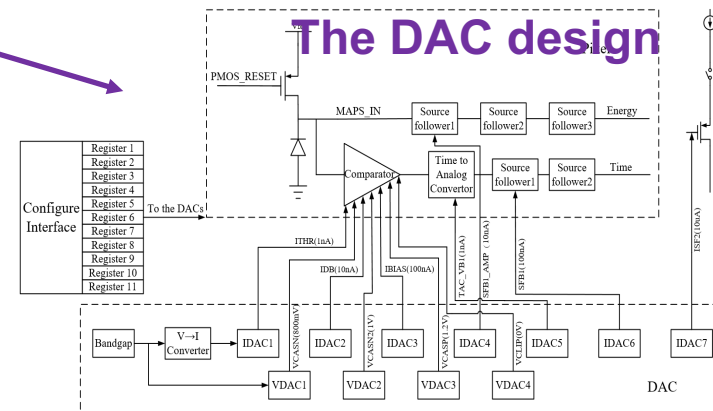


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- Octagon n-well is $3\mu\text{m} \times 3\mu\text{m}$

The Column-parallel ADC design



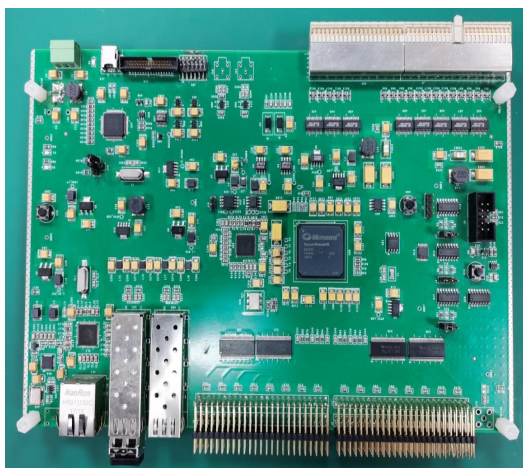
The DAC design



- 7 x 10bit VDAC + 4 x 8bit IDAC
- $3074\mu\text{m} \times 400\mu\text{m}$. With a voltage supply of 3.3V, the power consumption is 46.2mW.

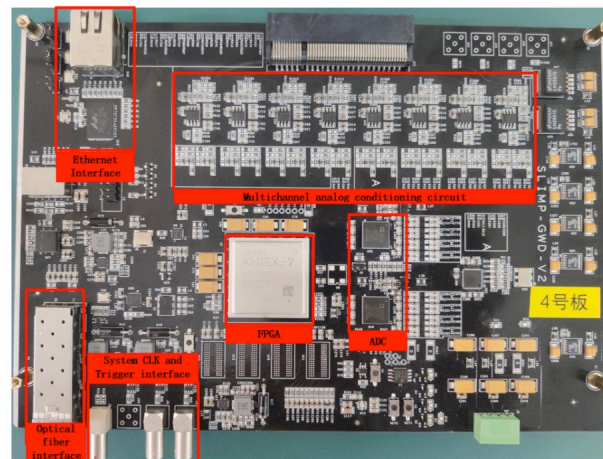
Radiation-hardened front-end electronics

Flash Based



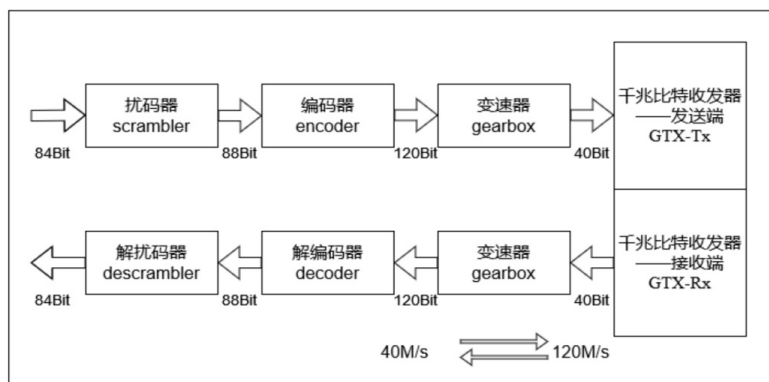
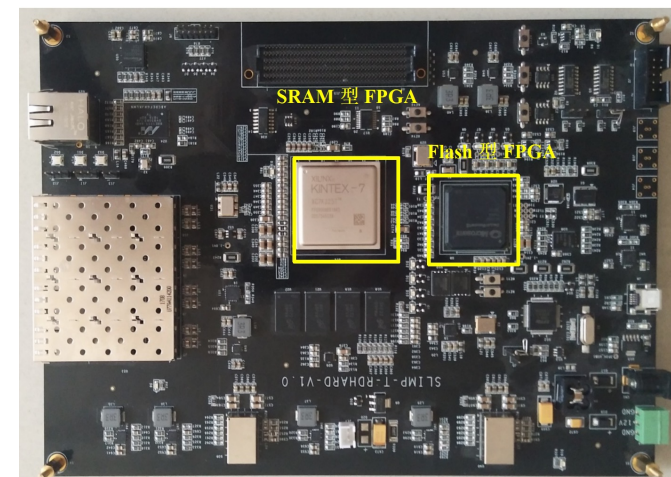
2.4Gbps

Sram Based

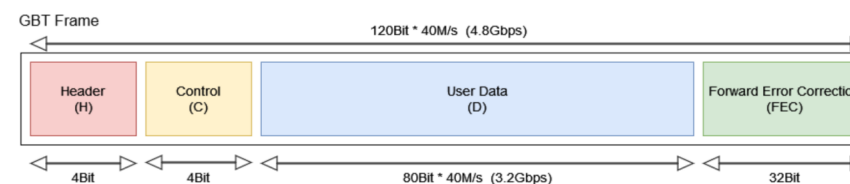


4.8Gbps

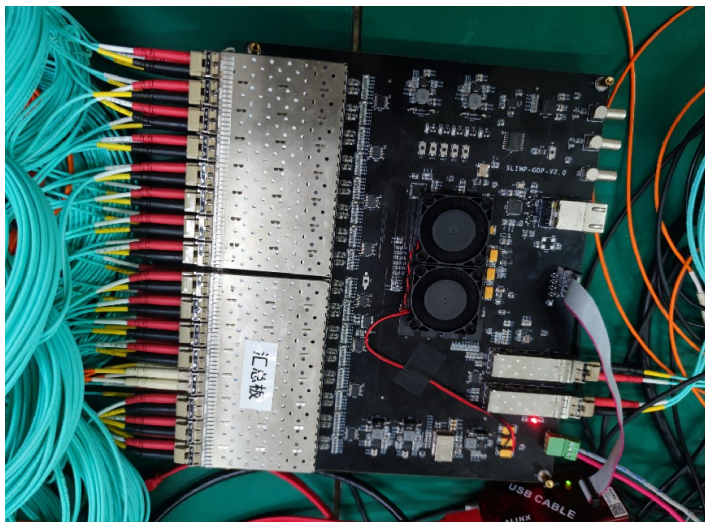
Sram based 三模重刷



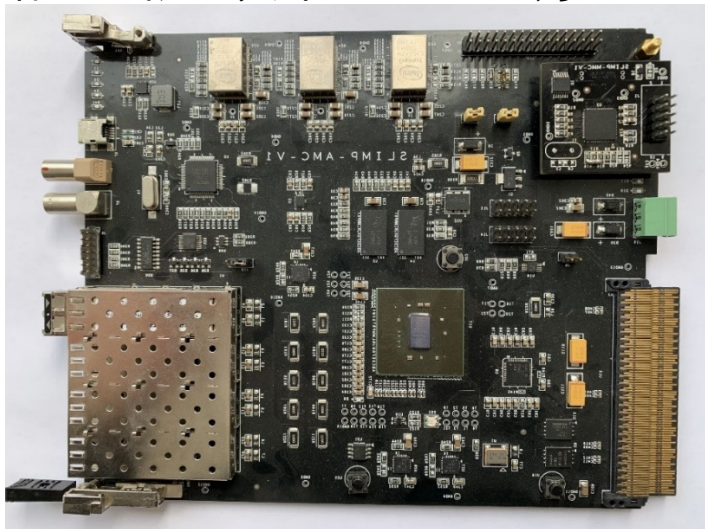
GBT-FPGA



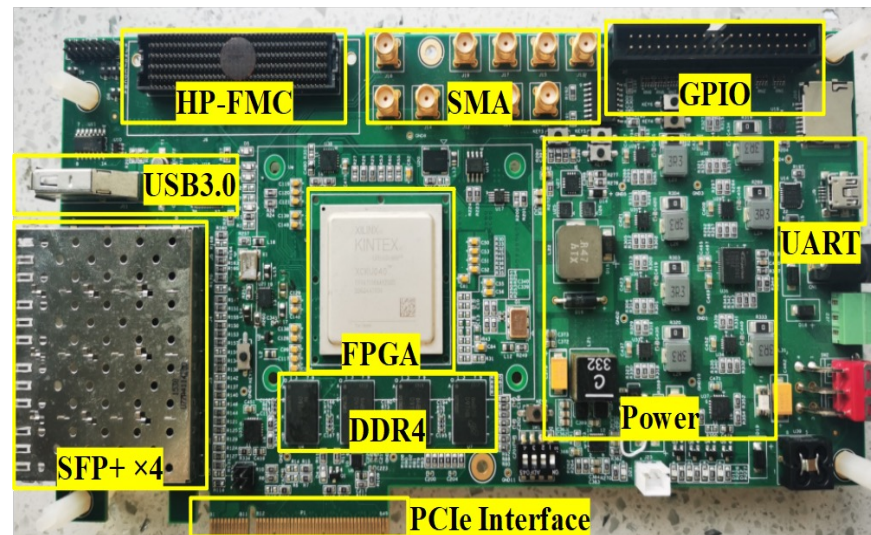
high speed back-end electronics



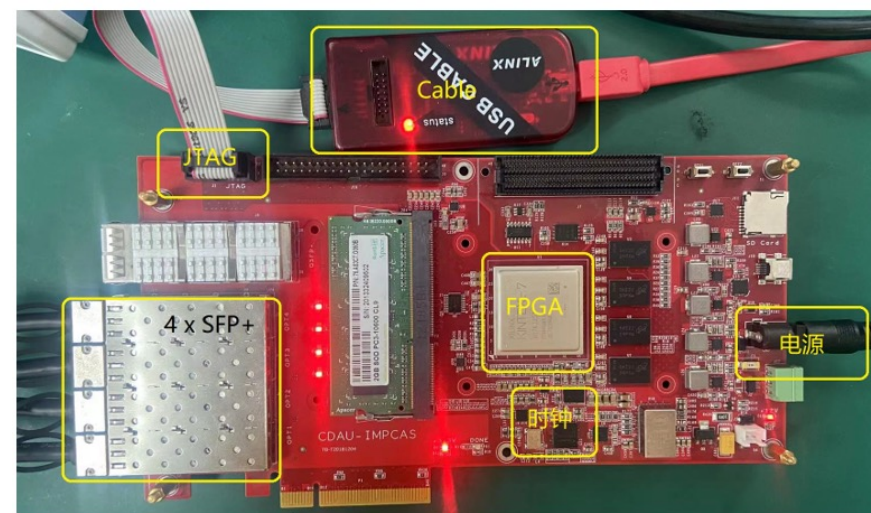
32路光纤汇总，两路万兆以太网数据汇总板。其中主要FPGA为Vertex-7。



MircoTCA的数据汇总板



ultra-scale的数据汇总板，其中PCIe提供了大于50gbps的数据通路



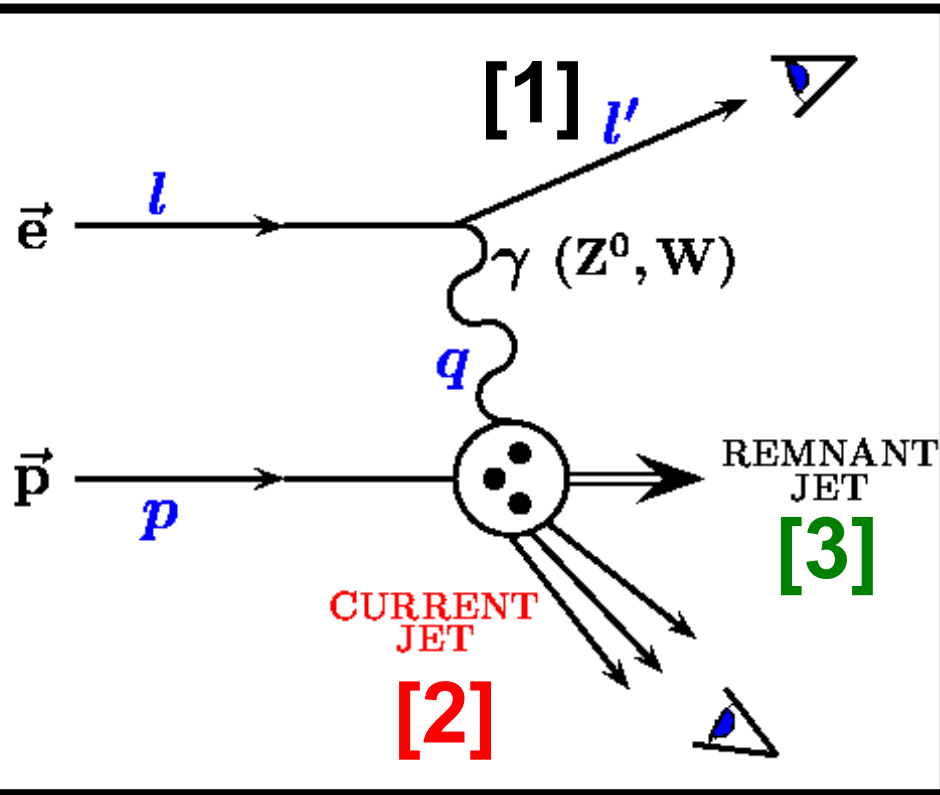
Summary

- Silicon + MPGD vertexing and tracking detector is designed to fit the requirement of EicC
- The full simulation of the geometry design is done to validate the performance
- The full functional MAPS based on domestic technology - Nupix-A1 is developed by IMP SLIMP & CCNU PLAC
- More efforts are needed to improve the R&D

Thanks for your attention!!

Backup

Lepton-Nucleon Scatterings



QED tool to study QCD nature of the nucleon

$$Q^2 = -q^2 = sxy$$

$$x = \frac{Q^2}{2p \cdot q}$$

$$y = \frac{p \cdot q}{p \cdot l}$$

$$s = 4E_e E_p$$

$$W = (q + p)^2$$

- QED probe is clean
- $\alpha_{EM} \sim 1/137$ with broad Q coverage
- One-photon exchange approximation:
~1% accuracy
- Detection scale is determined by Q^2 :
 $1\text{GeV}^2 \sim \text{nucleon size}$

Observe scattered electron/muon

[1]

→ inclusive

Observe current jet/hadron

[1]+[2]

→ semi-inclusive

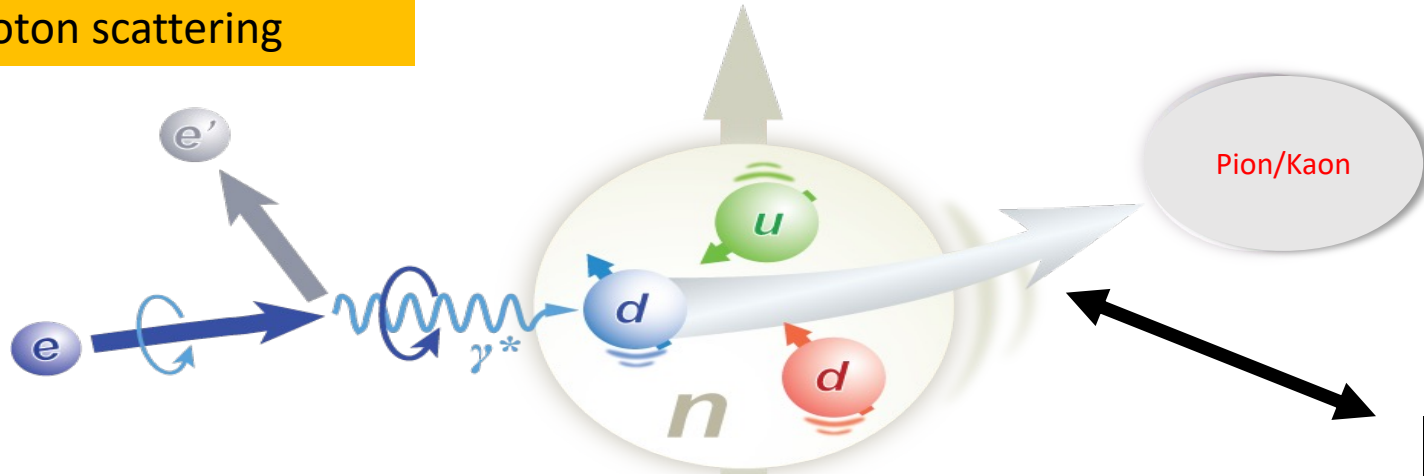
Observe remnant jet/hadron as well

[1]+[2]+[3]

→ exclusive

SIDIS processes for flavor decompositions

Electron-proton scattering



Experimental observable: polarized structure functions g_1

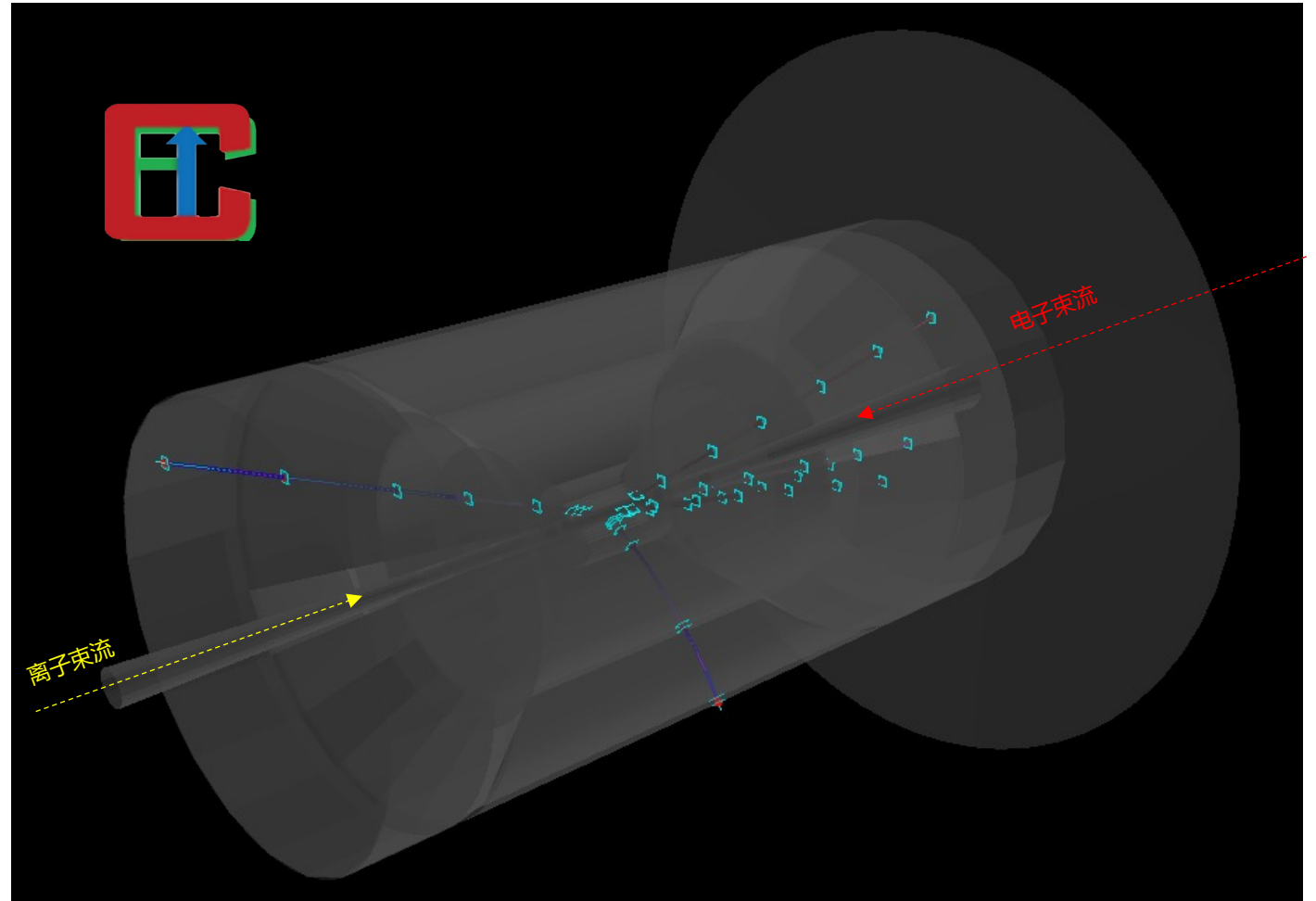
$$g_1^h(x, Q^2, z) = \frac{1}{2} \sum_q e_q^2 \left[\Delta q(x, Q^2) D_q^h(z, Q^2) + \Delta \bar{q}(x, Q^2) D_{\bar{q}}^h(z, Q^2) \right]$$

Leading Order picture

Extracted nucleon structure information: polarized PDFs (helicity distribution)

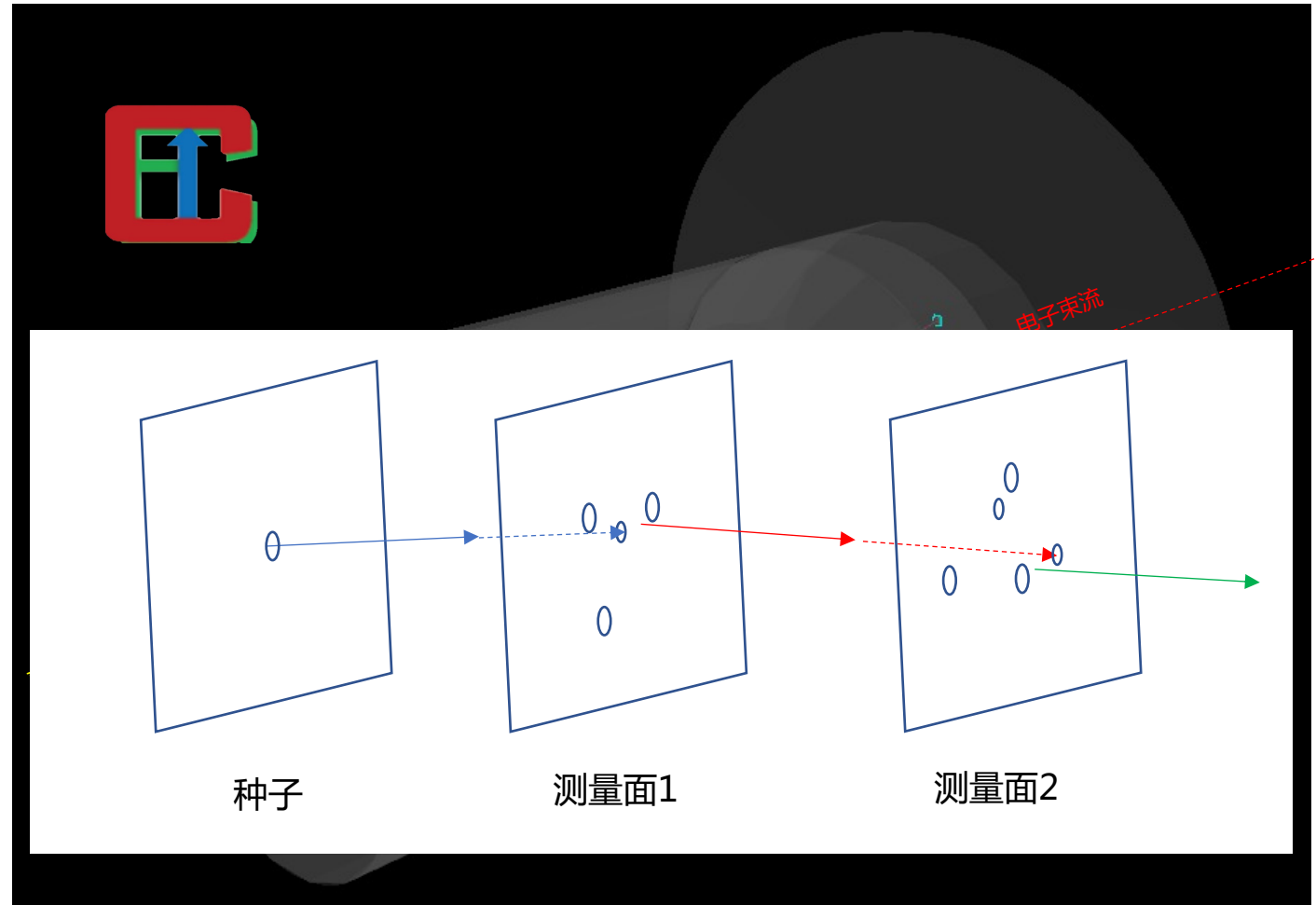
Track reconstruction

- No dedicated track finding algorithm is implemented
- Find track candidate according to the MC information
- Track candidates are fitted by Kalman fitter method



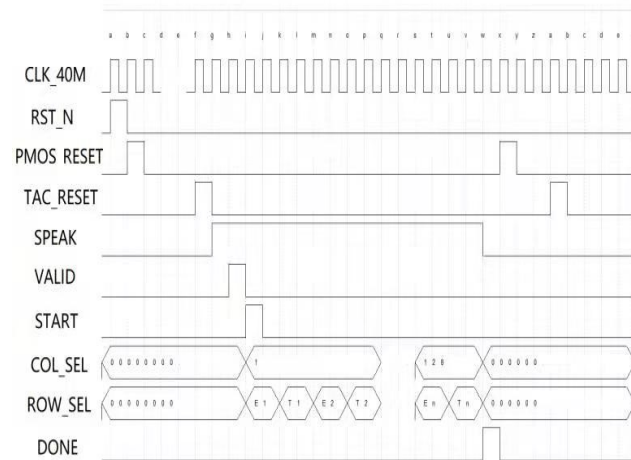
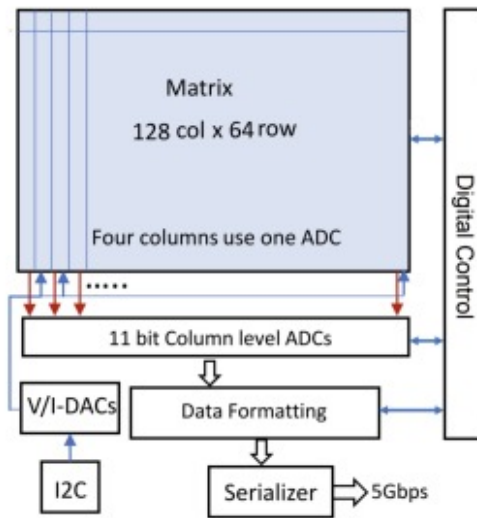
Track reconstruction

- No dedicated track finding algorithm is implemented
- Find track candidate according to the MC information
- Track candidates are fitted by Kalman filter method

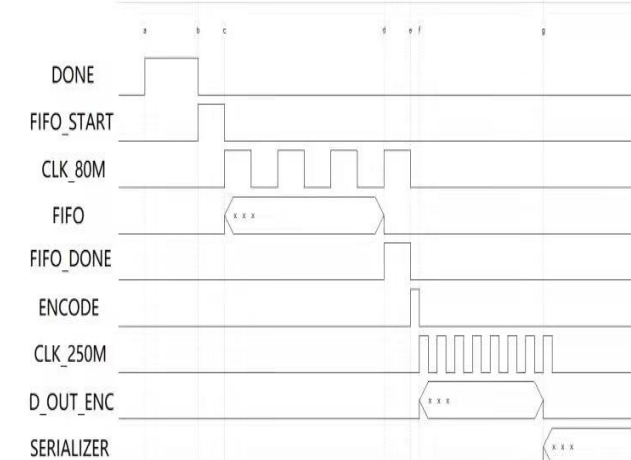


The Digital Control Design

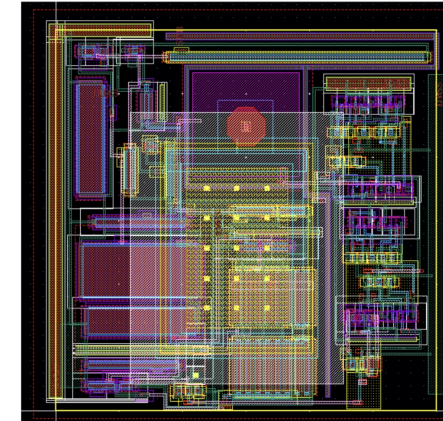
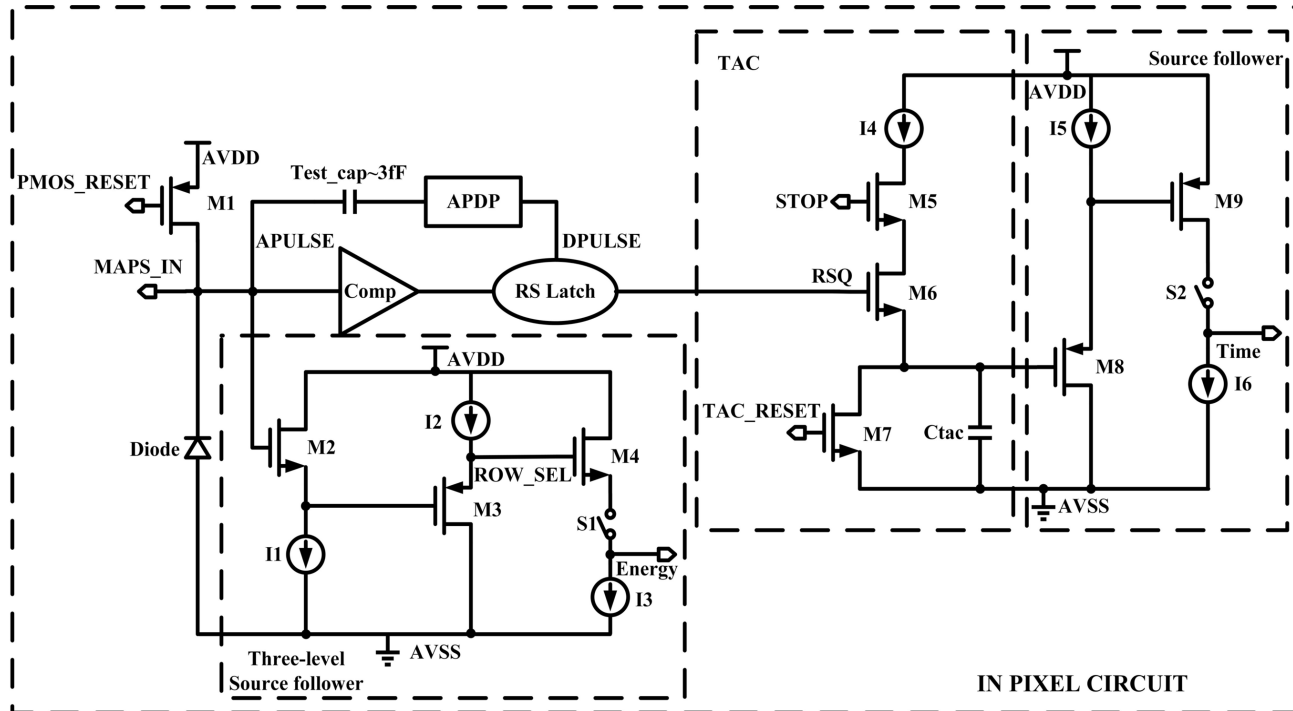
Pixel-to-pixel scan in each region



Chip-level data processing



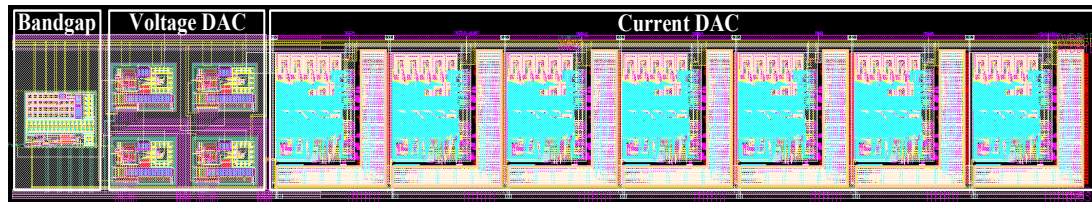
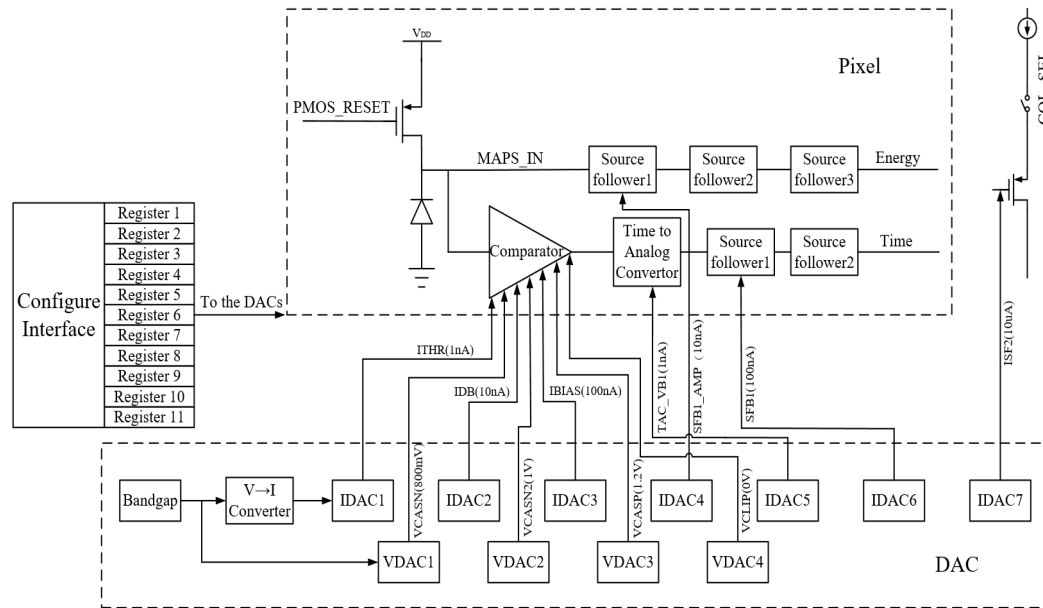
The Pixel Design



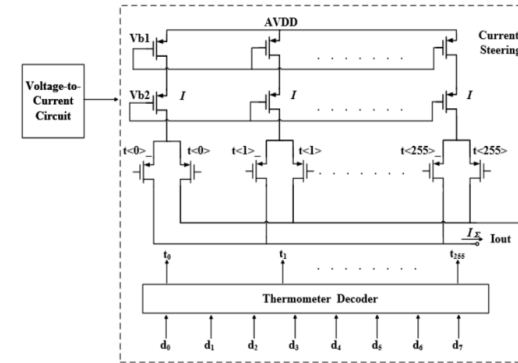
- Pixel Size $30\mu\text{m} \times 30\mu\text{m}$
- Diode area is $10\mu\text{m} \times 10\mu\text{m}$
- Octagon n-well is $3\mu\text{m} \times 3\mu\text{m}$

The DAC design

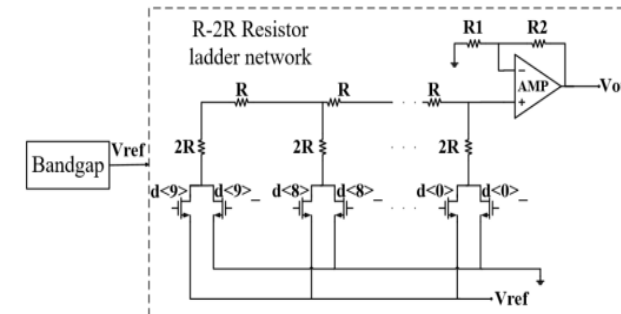
- 7 x 10bit VDAC + 4 x 8bit IDAC
- $3074\mu\text{m} \times 400\mu\text{m}$. With a voltage supply of 3.3V, the power consumption is 46.2mW.



- 8-bit current-steering type DAC

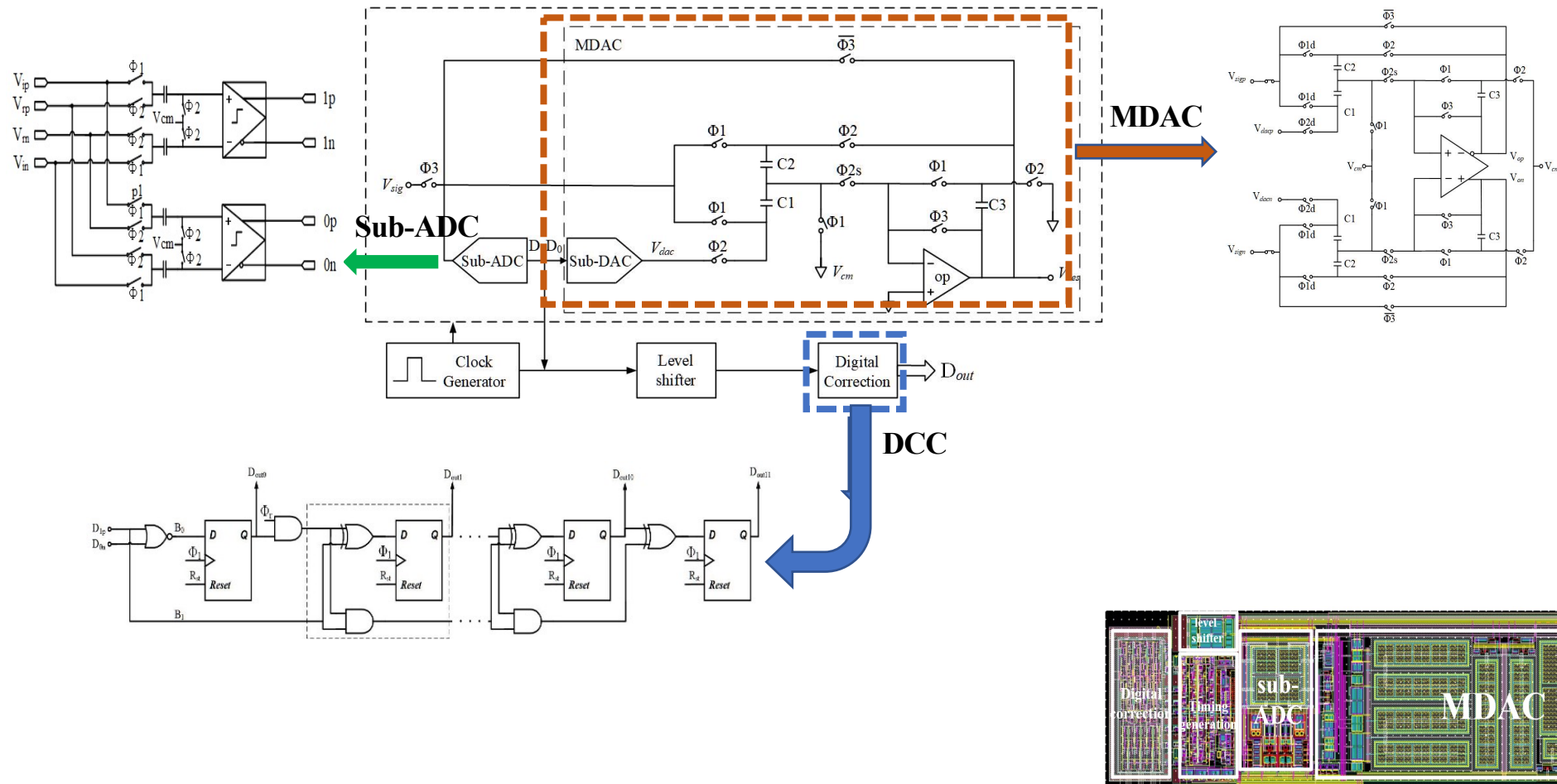


- 10-bit R-2R voltage DAC



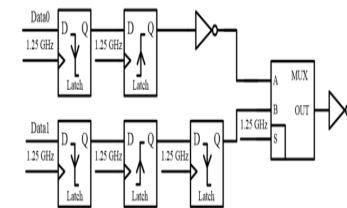
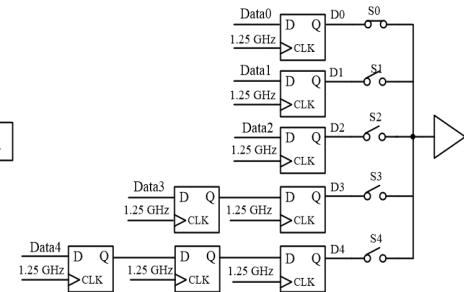
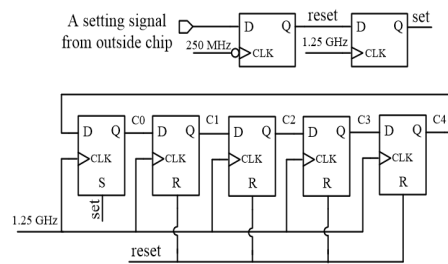
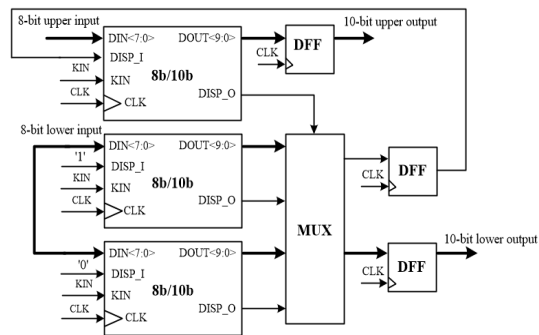
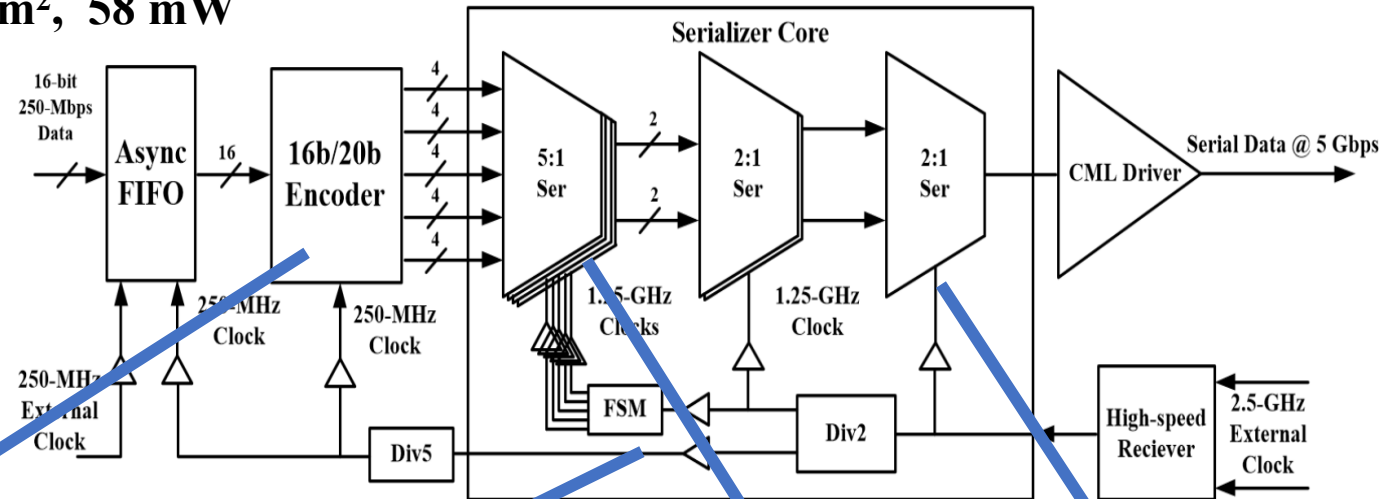
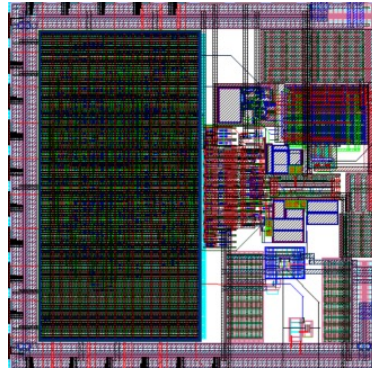
The Column-parallel ADC design

- Designed in a fully differential cyclic architecture and takes 11 clock cycles to generate 12bit output
- 3.63Msps x 12bit, $380 \times 100 \mu\text{m}^2$, 7.6mW@3.3V



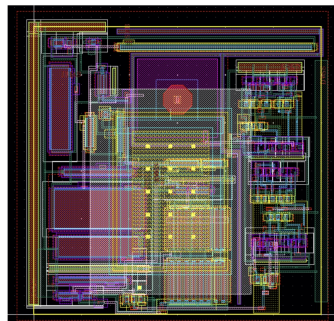
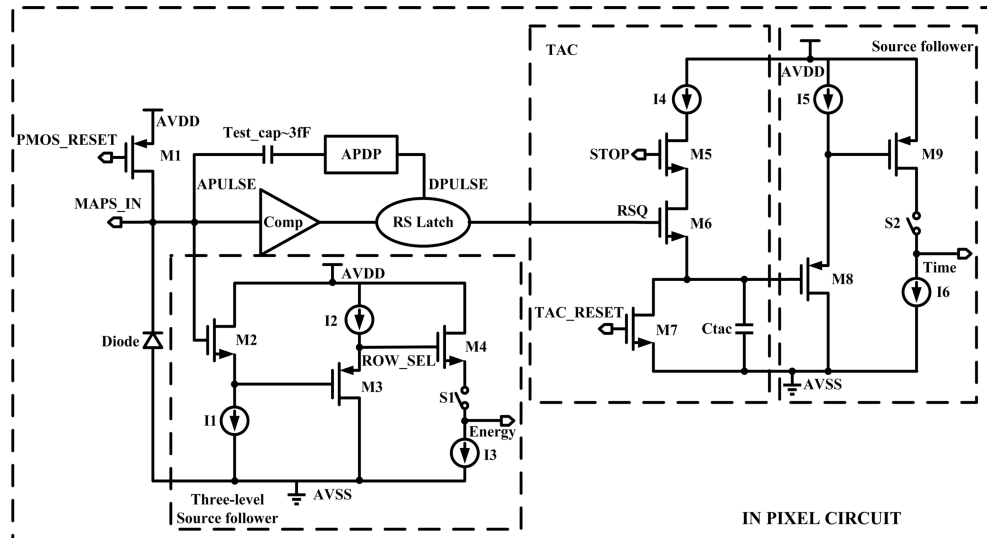
The Serializer Design

➤ 5Gbps, 1.96 mm², 58 mW



The Pixel and DAC design

The Pixel Design



- Pixel Size $30\mu\text{m} \times 30\mu\text{m}$
- Diode area is $10\mu\text{m} \times 10\mu\text{m}$
- Octagon n-well is $3\mu\text{m} \times 3\mu\text{m}$

The DAC design

- 7 x 10bit VDAC + 4 x 8bit IDAC
- $3074\mu\text{m} \times 400\mu\text{m}$. With a voltage supply of 3.3V, the power consumption is 46.2mW.

